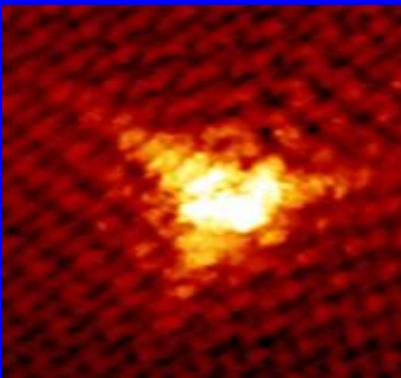
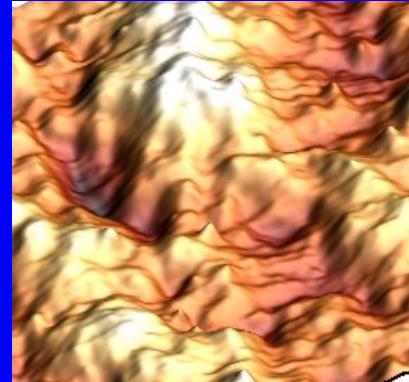


Interaction of Dirac electrons with spins and point charges

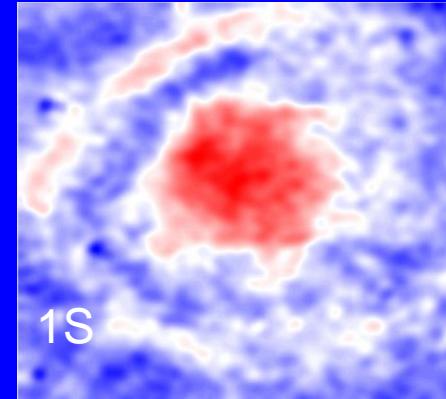
Vacancies in
graphene



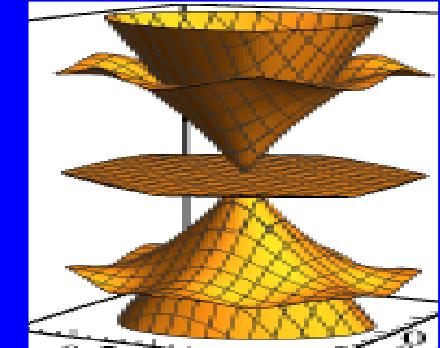
Vacancy Magnetic
moment and
Kondo screening



Vacancy Charge
and Tunable
artificial atom



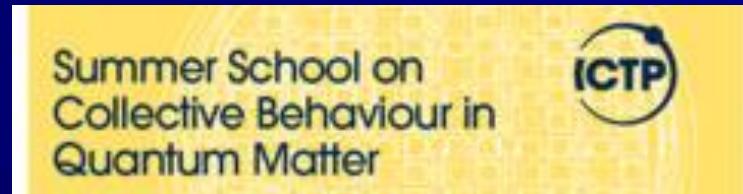
Twisted bilayer
graphene



Eva Y. Andrei

LECTURE NOTES POSTED AT:

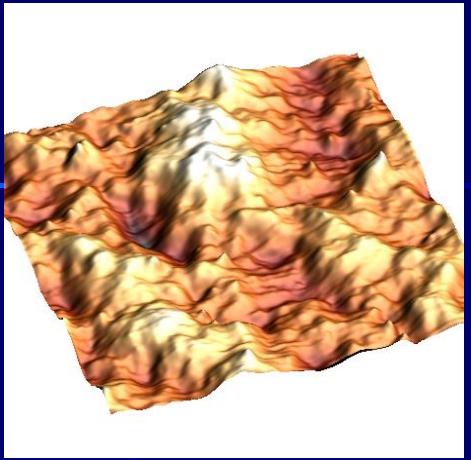
<http://www.physics.rutgers.edu/~eandrei/links.html#trieste18>



E.Y. Andrei



Scanning tunneling microscopy and spectroscopy



❖ Engineering electronic properties

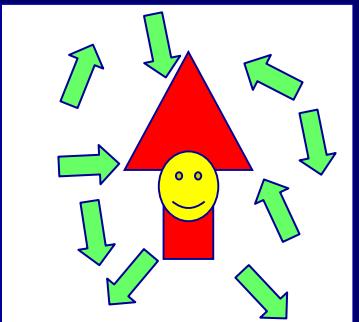
- Density of states and Landau levels in graphene
- Scanning tunneling microscopy (STM) and spectroscopy (STS)
- Defects:
 - Atomic collapse and artificial atom
 - Kondo effect
- Substrate:
 - Twisted graphene



Kondo Screening of Impurity Moments in Metals

$T > T_K$

Unscreened



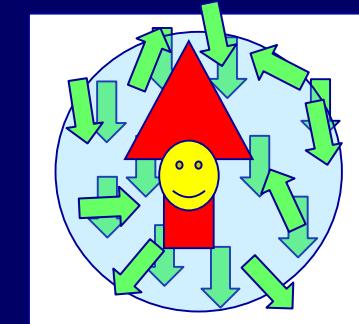
J antiferromagnetic
coupling to electron bath

$$T_K \propto \exp(-1 / \rho J)$$

ρ density of states at E_F

$T < T_K$

Screened



$$\rho(E_F) > 0, J > 0 \rightarrow T_K > 0$$

- ❖ Normal metals $\rho(E_F) \sim \text{finite}; J \neq 0 \quad \rightarrow T_K > 0$
- ❖ Insulators $\rho(E_F) = 0 \quad \text{No Kondo screening}$

What happens in a pseudogap system?



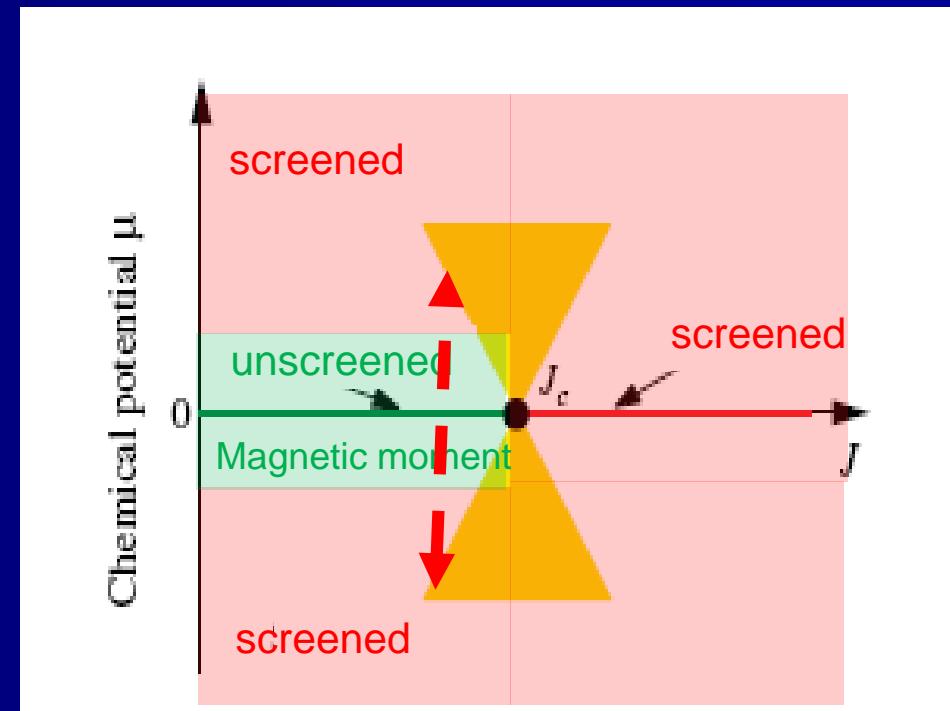
Kondo Screening in pseudo-gap systems

- Pseudo- gap systems $\rho(E) \propto E^r$ screening suppressed.
 - ❖ $r = 1$ (graphene, high T_c superconductors)

$\mu \sim 0$ (undoped)
• Kondo screening only for $J > J_c$
• J_c finite only for asymmetric DOS

- $|\mu| > 0$ doped
- Normal Kondo screening

- D. Witchoff and E. Fradkin, Phys. Rev. Lett. 64, 1835(1990)
- K. Chen and C. Jayaprakash, J. Phys L491 (1995)
- K. Ingersent, Phys. Rev. B54, 11936 (1996)
- C. Cassanello and E. Fradkin , (1996)
- R. Bulla, T. Pruschke, and A. C. Hewson, (1998)
- Polkovnikov A., Phys. Rev. B, 65 (2002) 064503
- Vojta M. and Fritz L., Phys. Rev. B, 70 (2004) 094502.
- Vojta, Fritz, Bulla EPL (2010)
- PW Lo, GY Guo, F. Anders, arXiv:1402.0040



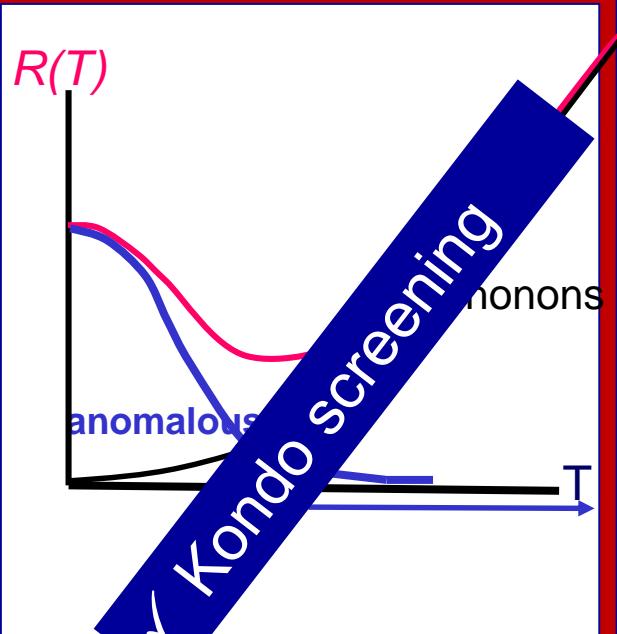
Electrical tuning of magnetic moment





Kondo Screening Experimental Signatures

Resistance minimum



nature
physics

LETTER

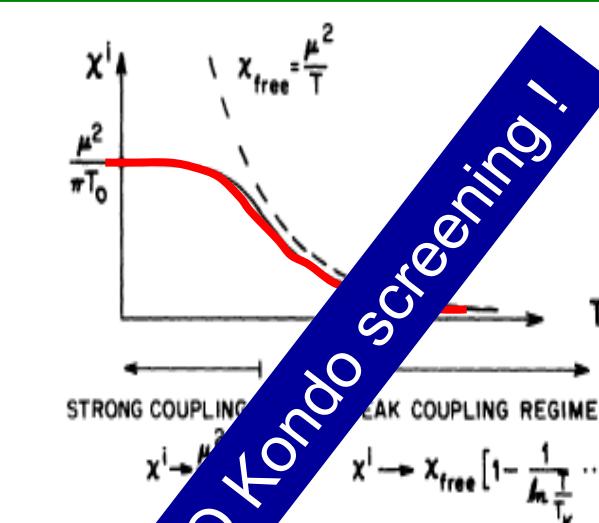
PUBLISHED ONLINE: 3 APRIL 2011 | DOI:10.1038/NPHYS2181

Tunable Kondo effect in graphene with defects

Jian-Hao Chen^{1,2†}, Liang Li², William G. Cullen^{1,2}, Ellen D. Williams^{1,2} and Michael S. Fuhrer^{1,2*}

Measures:
scattering off Kondo cloud

Magnetization saturation



nature
physics

LETTERS

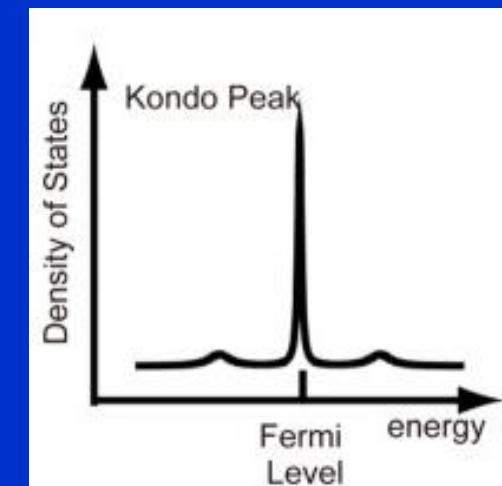
PUBLISHED ONLINE: 10 JANUARY 2012 | DOI:10.1038/NPHYS2518

Spin-half paramagnetism in graphene induced by point defects

R. R. Nair¹, M. Sepioni¹, I-Ling Tsai¹, O. Lehtinen², J. Keinonen², A. V. Krasheninnikov^{2,3}, T. Thomson⁴, A. K. Geim¹ and I. V. Grigorieva^{1*}

Measures:
Unscreened moment

DOS – Kondo Peak



- Kondo Peak at E_F
- Low T linewidth Γ

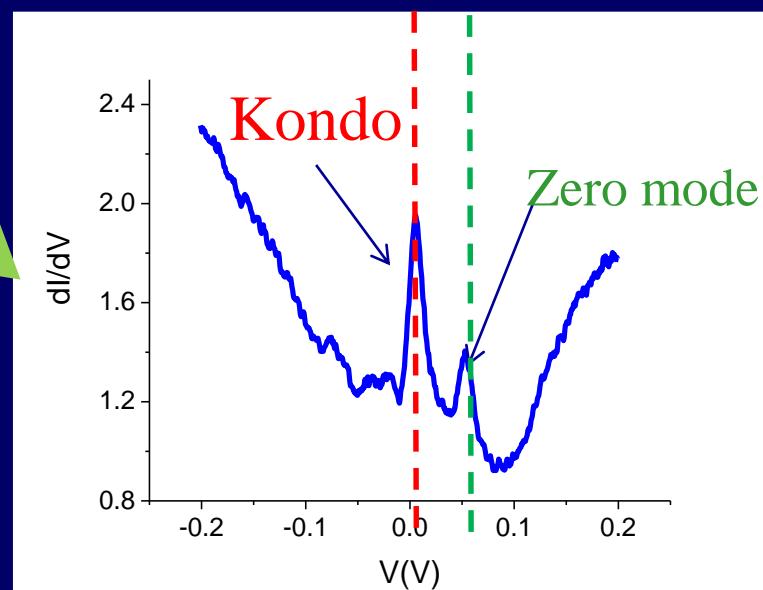
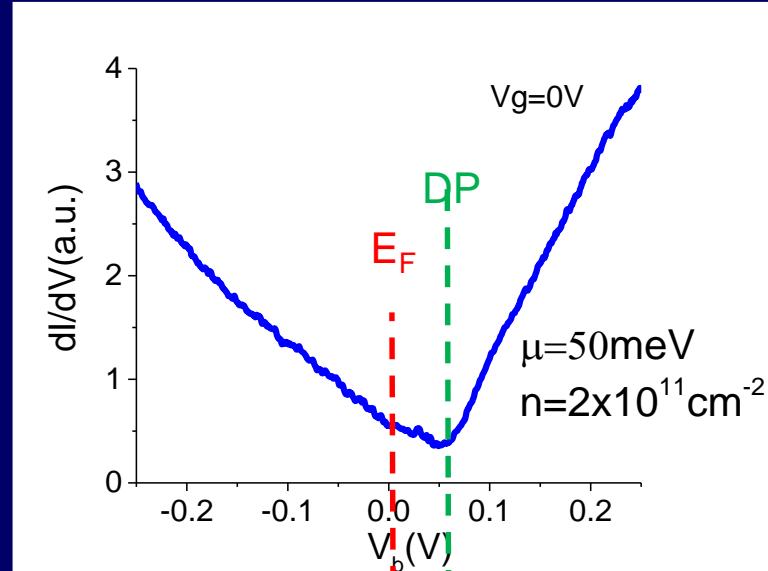
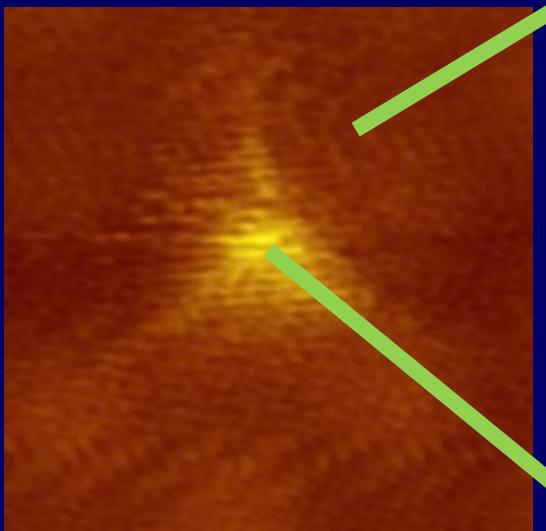
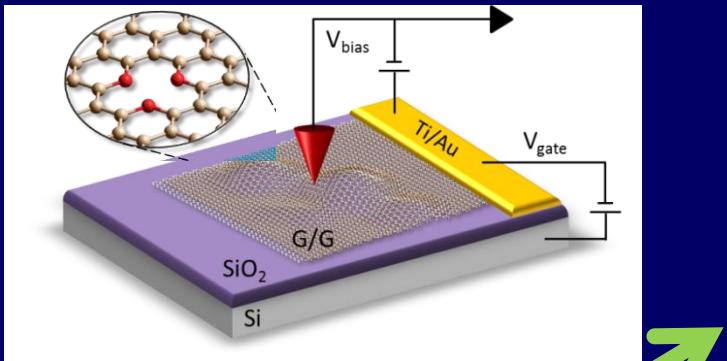
$$k_B T_K \sim \Gamma/2$$

DOS enhancement at E_F

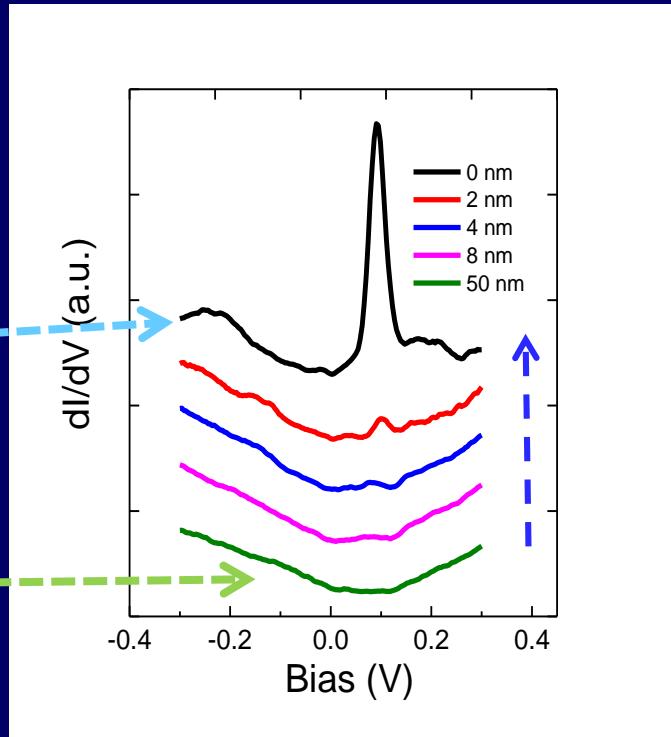
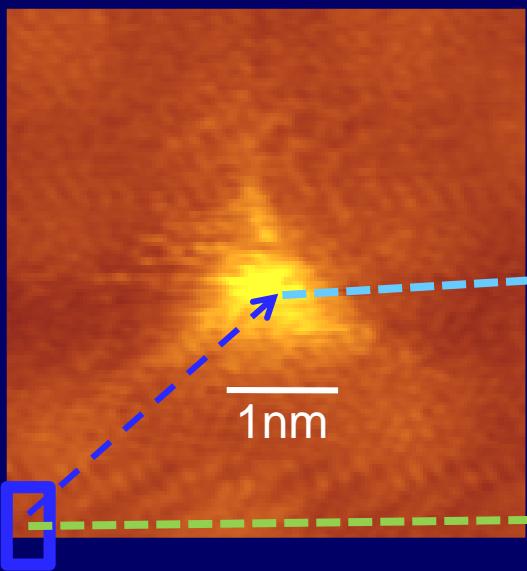
E.Y. Andrei



Vacancy in graphene



Vacancy Peak

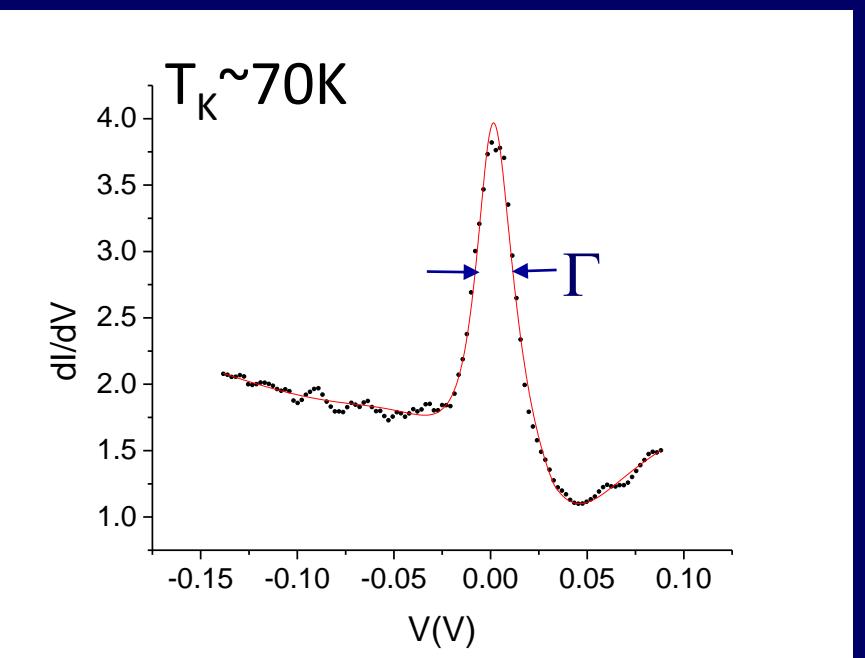


Vacancy Peak

- localized on vacancy site <2nm.
- pinned to the Dirac point



Kondo Temperature

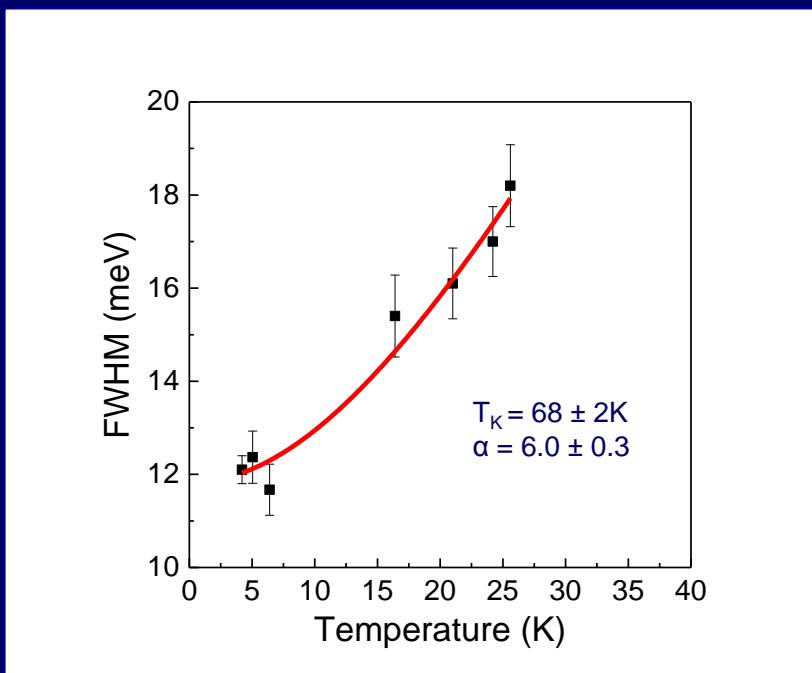


Fit to Fano lineshape

$$\frac{dI(V)}{dV} = A \frac{(\varepsilon + q)^2}{1 + \varepsilon^2} + B$$

$$\varepsilon = \frac{E - \varepsilon_0}{\Gamma/2}$$

$$k_B T_K \sim \Gamma/2$$



Fit to T dependence

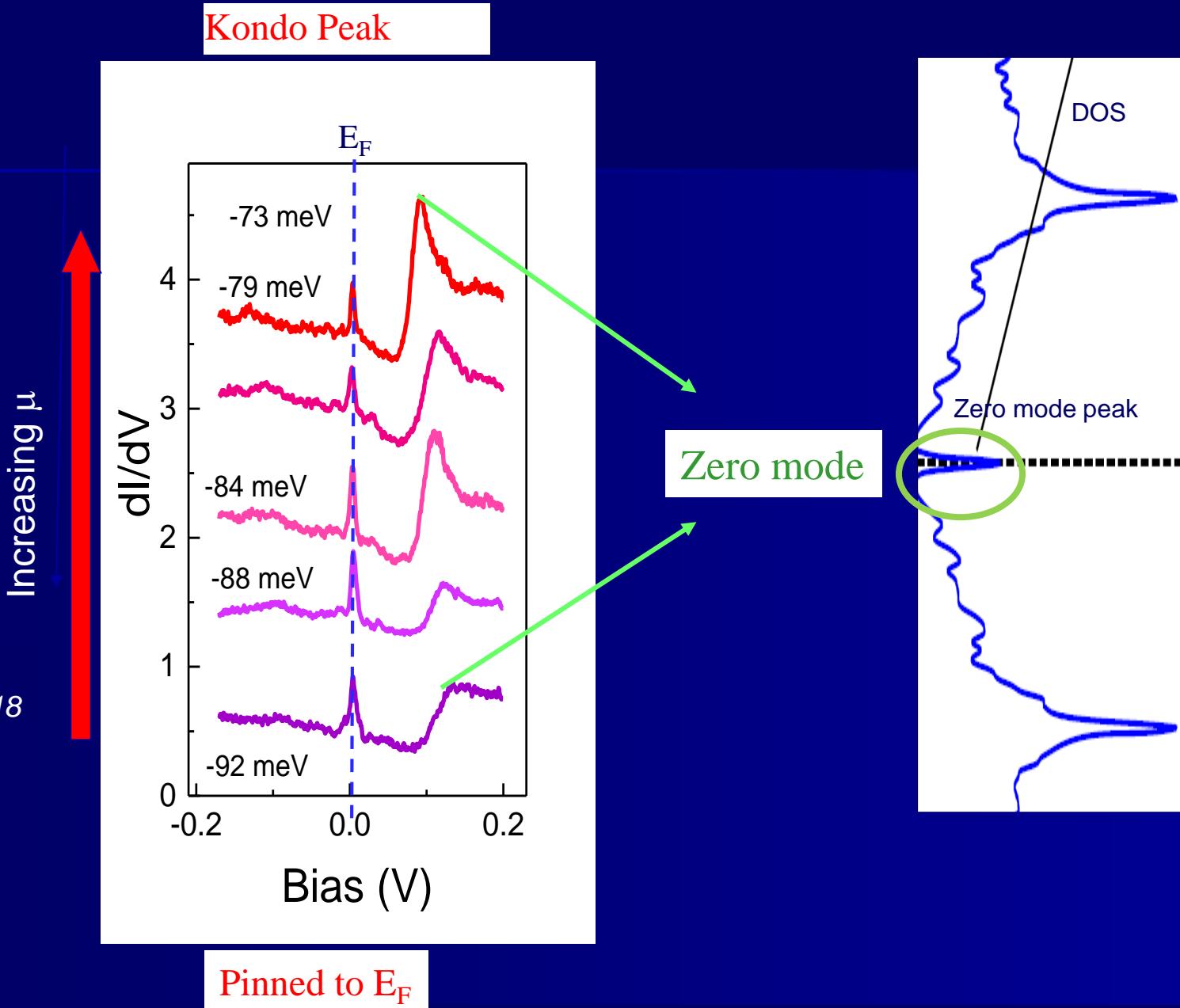
$$\Gamma = \sqrt{(\alpha k_B T)^2 + (2k_B T_K)^2}$$

- O. Újsághy, et al. Solid State Commun. **117**, 167(2001)
A.S. Zyazin, et al. Synthetic Metals **161**, 591 (2010)
M. Ternes, et.al. J. Phys.: Condens. Matter 21, 053001, (2009)

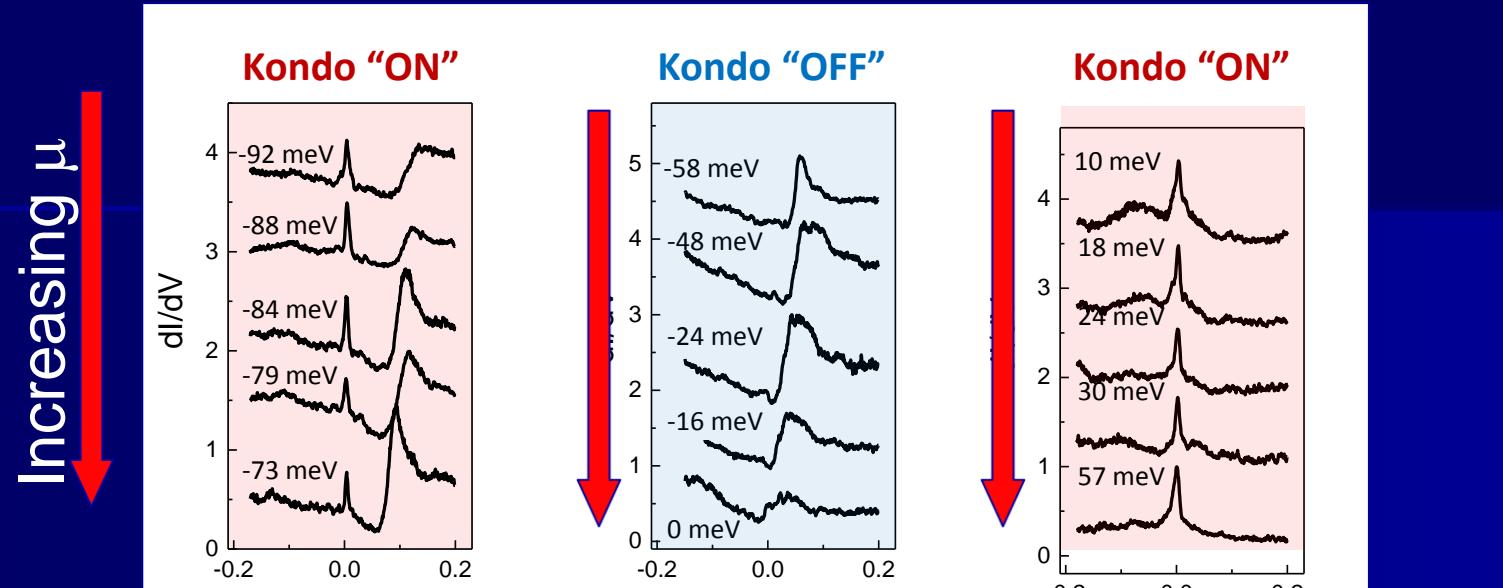


Gate Dependence

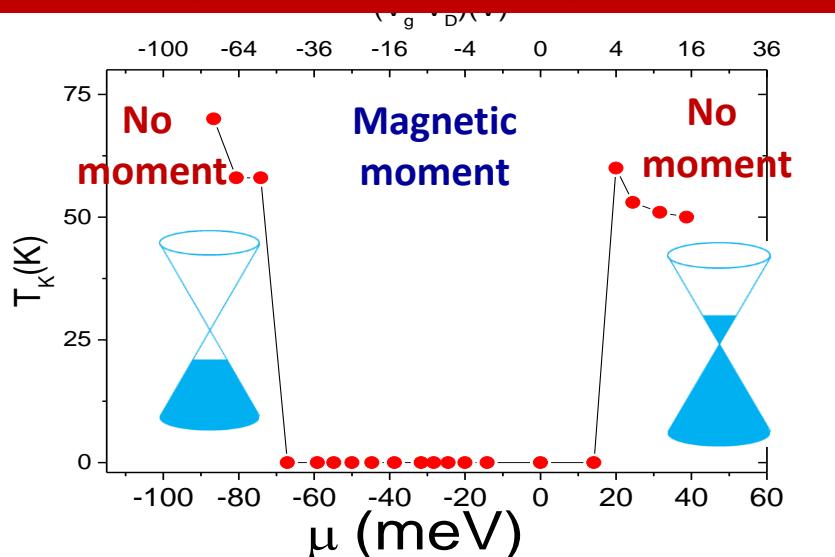
J. Mao et al
Nature Communications 2018



Reentrant Kondo Screening



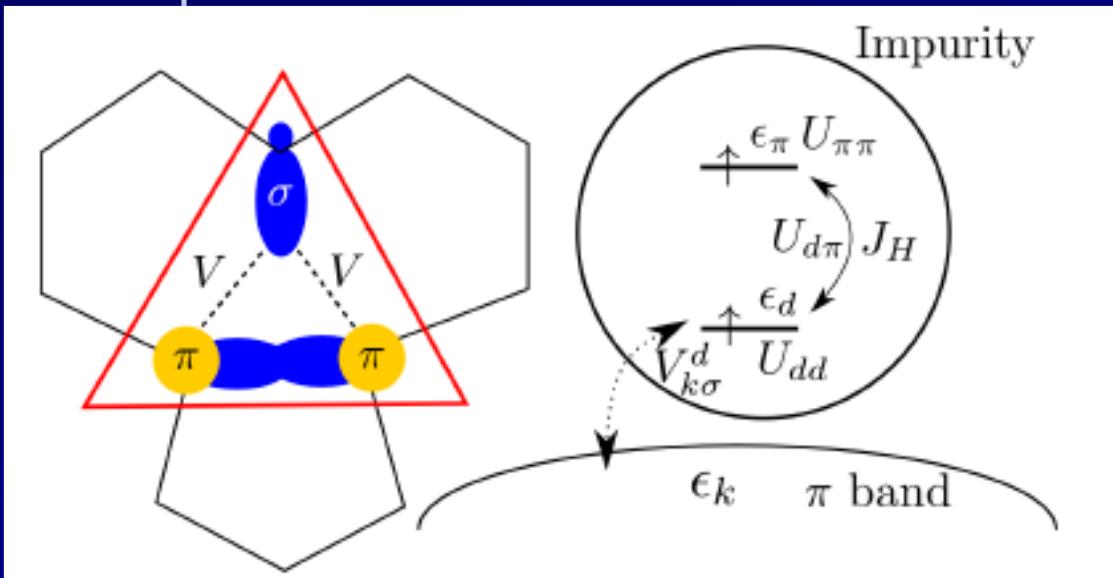
Electrically tuned magnetic moment



$J < J_c$

Model for Kondo screening of vacancy moment

- Anderson impurity model
- Numerical renormalization group calculations



- bare σ -orbital energy
- On site Coulomb
- Exchange coupling
- Hund coupling
- Critical coupling

$$\begin{aligned}\varepsilon_d &= -1.6 \text{ eV} \\ U_{dd} &= 2 \text{ eV} \\ U_{d\pi} &= 0.1 \text{ eV} \\ J_H &\sim -0.35 \text{ eV} \\ \Gamma_c &= 1.15 \text{ eV}\end{aligned}$$

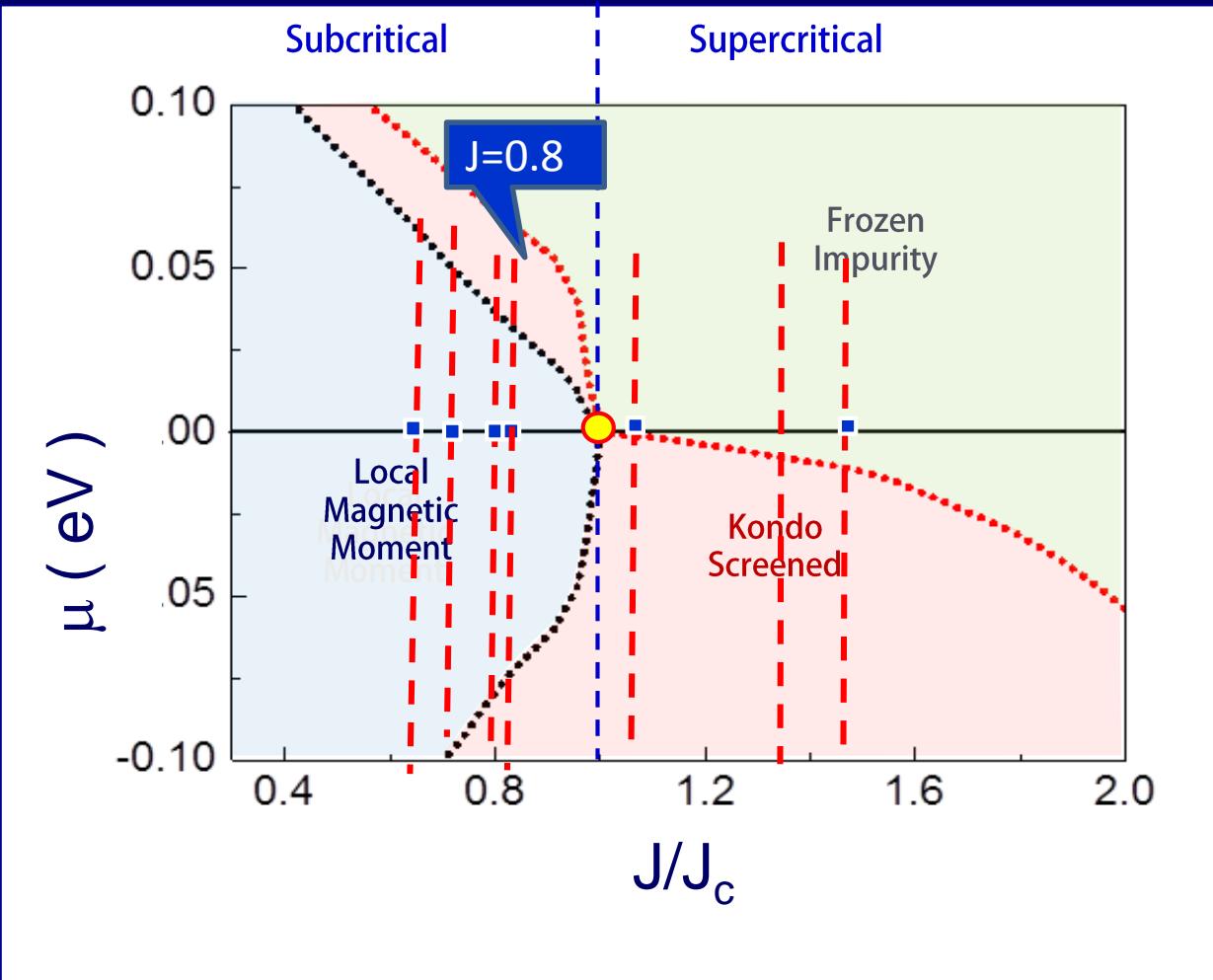
Single orbital approximation:

$$U_{eff}(\mu) = \begin{cases} U_{dd} & \mu \leq 0 \\ U_{dd} + \min(U_{d\pi}, \alpha\mu) & \mu > 0 \end{cases}$$



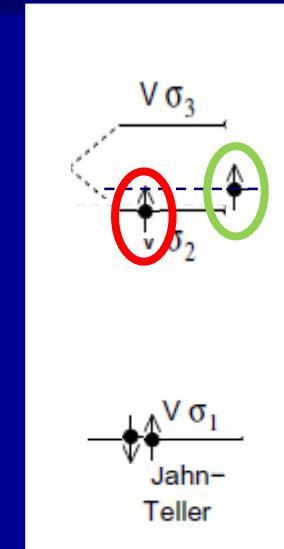
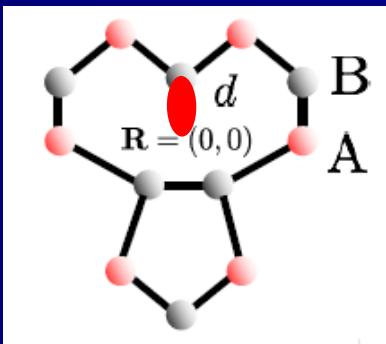
Kondo Screening Phase Diagram

Numerical Renormalization Group



What determines J ?

- σ Dangling bond \mapsto localized state $\mapsto 1\mu_B$



➤ σ state (in plane) – orthogonal to π conduction electrons $\mapsto J=0$

➤ p_z state – Ferromagnetic coupling $\mapsto J=0$

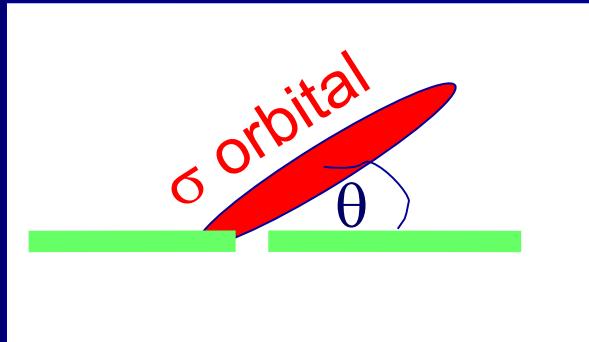
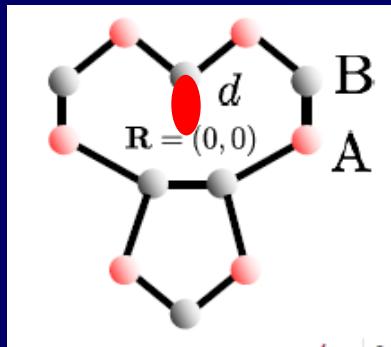
$J=0 \mapsto$ NO KONDO SCREENING !!

Can J be Finite in Graphene?

Local Moment Formation and Kondo Effect in Defective Graphene

M. A. Cazalilla,^{1,2} A. Iucci,³ F. Guinea,⁴ and A. H. Castro Neto²

- Out of plane distortion of dangling bond
- ↪ Finite AF coupling with conduction electrons ↪ Kondo screening



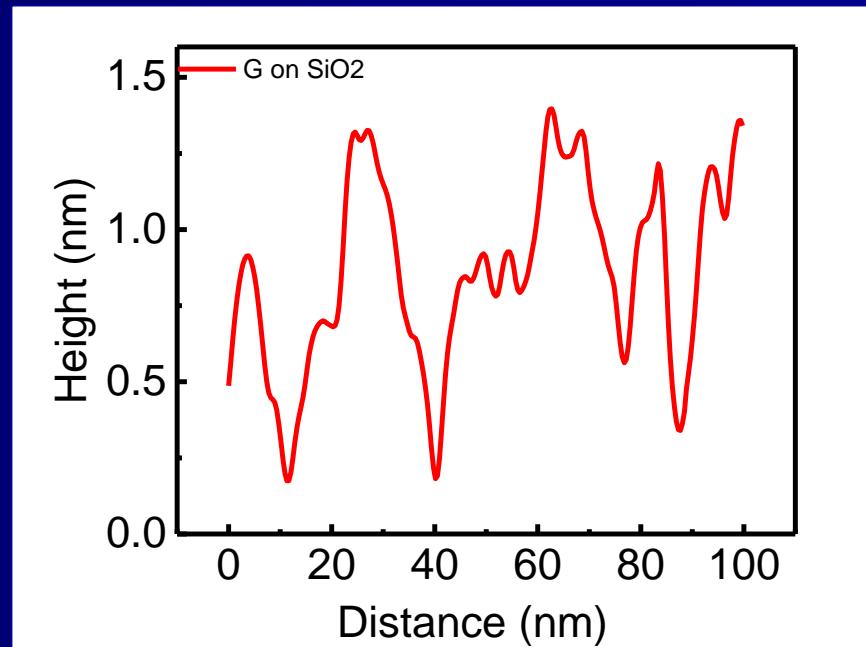
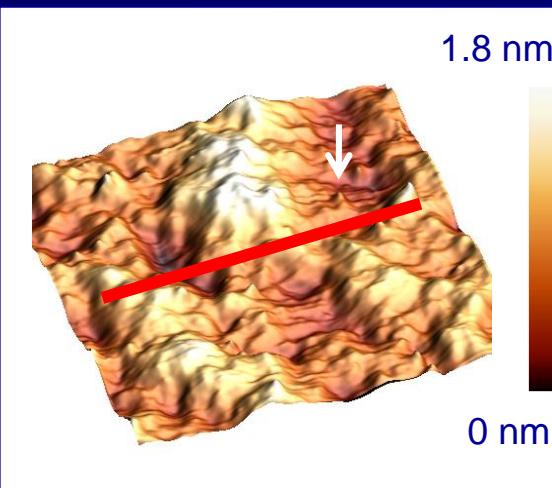
$$J \sim \sin \theta$$

Finite Kondo coupling

Corrugated Substrate ??

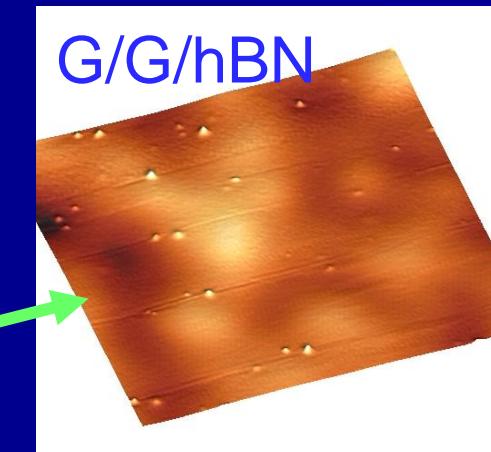
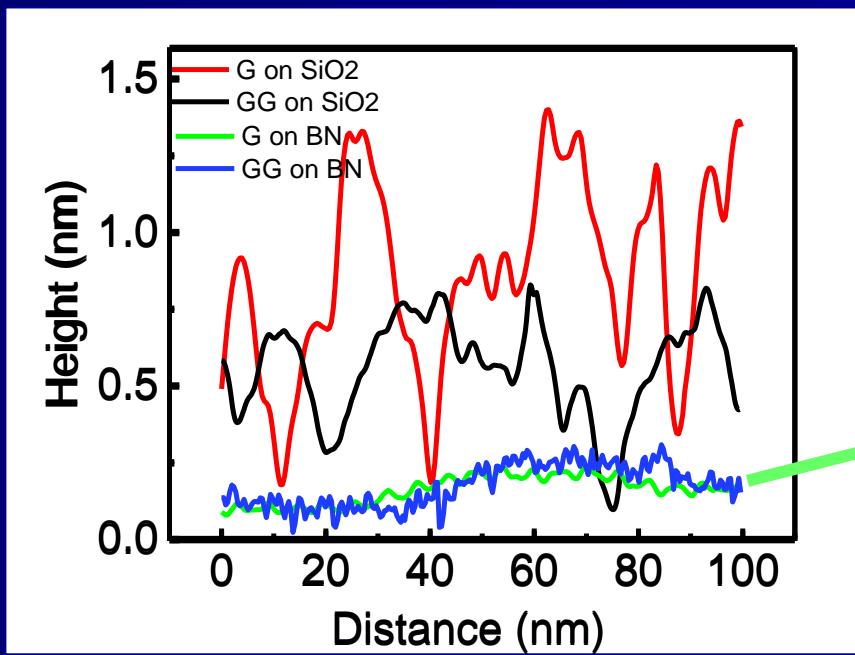
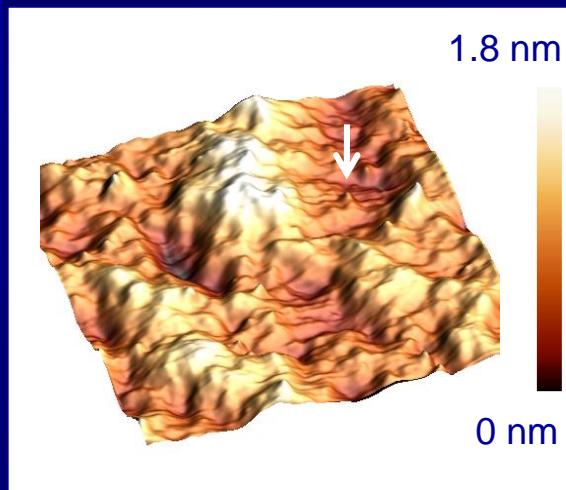
Substrate corrugation and Kondo screening

Substrate Corrugation	G/SiO ₂ 2nm
Maximum T _K	T _K ~180K
% of screened vacancies	Most



Substrate corrugation and Kondo screening

Substrate Corrugation	G/SiO ₂ 2nm	G/G/SiO ₂ 1nm	G/hBN 0.2nm	G/G/hBN 0.2nm
Maximum T _K	T _K ~180K	T _K ~ 70K	No Kondo	No Kondo
% of screened vacancies	Most	30%	none	none



Global Measurements and Conflicting results

nature
physics

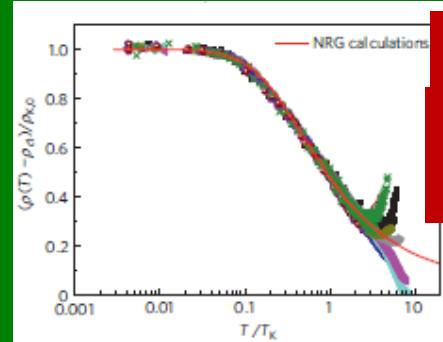
LETTERS

PUBLISHED ONLINE: 3 APRIL 2011 | DOI:10.1038/NPHYS1962

Tunable Kondo effect in graphene with defects

Jian-Hao Chen^{1,2†}, Liang Li², William G. Cullen^{1,2}, Ellen D. Williams^{1,2} and Michael S. Fuhrer^{1,2*}

- $R(T) \mapsto$ Kondo screening
➤ T_K 20-70K



Need Local measurement

Y Jiang et al Nature Communications 2018
D. May et al Phys. Rev. B 97, 155419 (2018)

Measures:

Scattering off Kondo cloud

- Sensitive to screened Moments only.

nature
physics

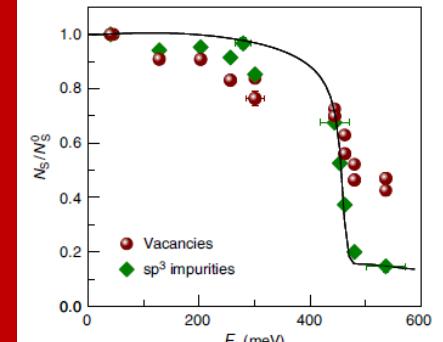
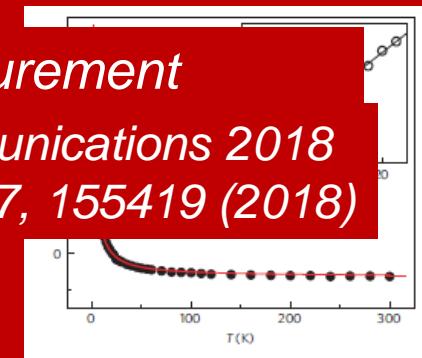
LETTERS

PUBLISHED ONLINE: 10 JANUARY 2012 | DOI:10.1038/NPHYS2183

Spin-half paramagnetism in graphene induced by point defects

R. R. Nair¹, M. Sepioni¹, I-Ling Tsai¹, O. Lehtinen², J. Keinonen², A. V. Krasheninnikov^{2,3}, T. Thomson¹, A. K. Geim¹ and I. V. Grigorieva^{1*}

- $\chi(T) \mapsto$ No Kondo screening
- Moments unscreened at low T



Measures:

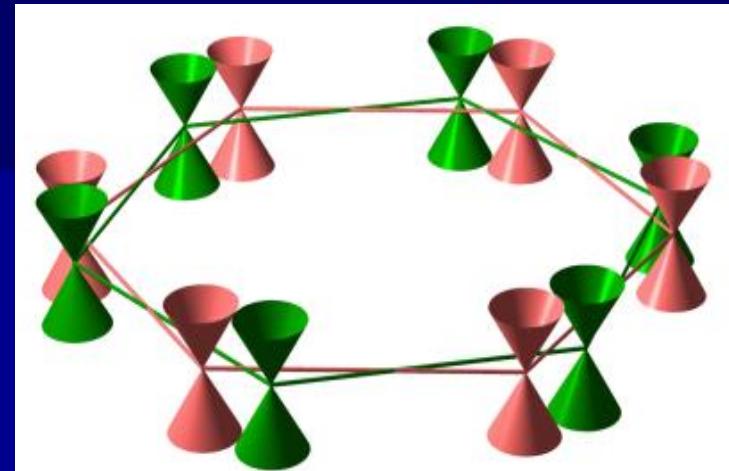
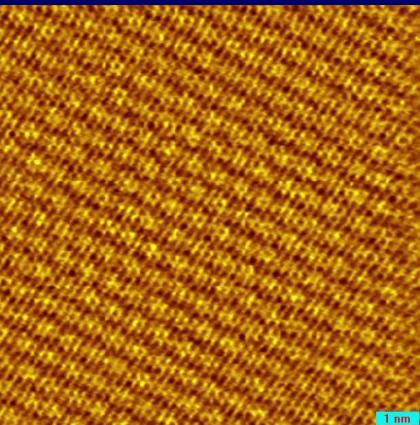
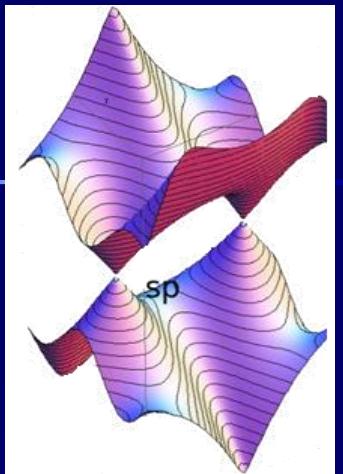
Magnetic moments

- Sensitive to unscreened Moments only.

➤ Global measurements probe complementary properties



Graphene with a twist

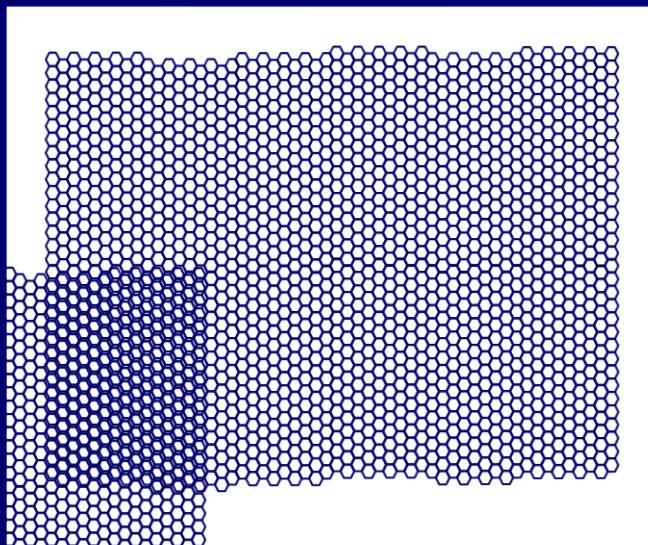


- ❖ Engineering electronic properties
 - Density of states
 - Landau levels in graphene
 - Scanning tunneling microscopy (STM) and spectroscopy (STS)
 - Atomic collapse and artificial atom
 - Kondo effect
 - Twisted graphene

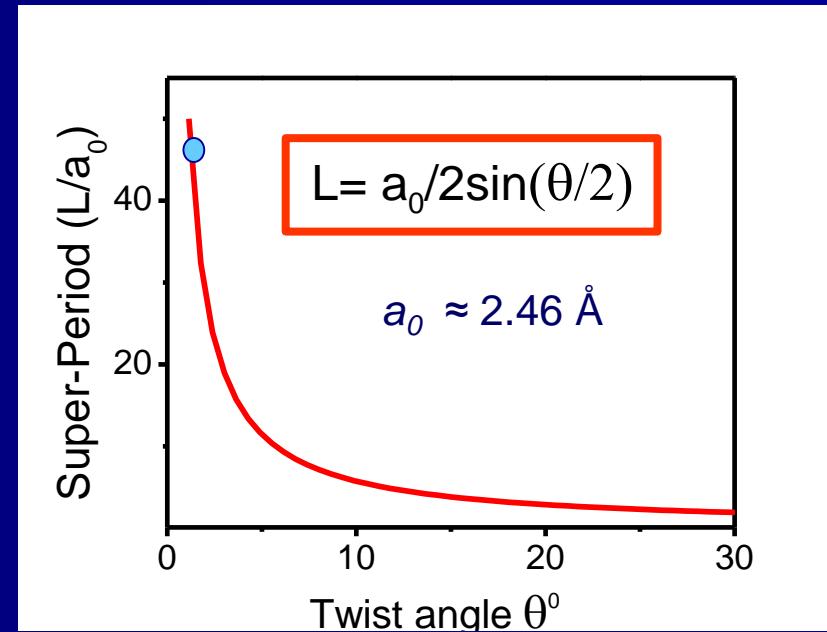
Twisted graphene – Moiré patterns

Twist between layers \mapsto Moiré pattern:

$$\theta = 3^\circ$$



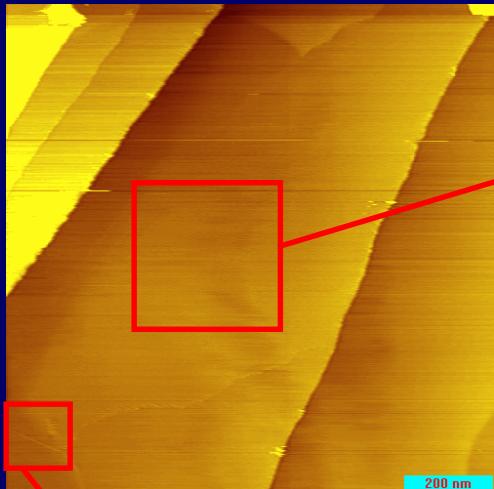
Superstructure with period L



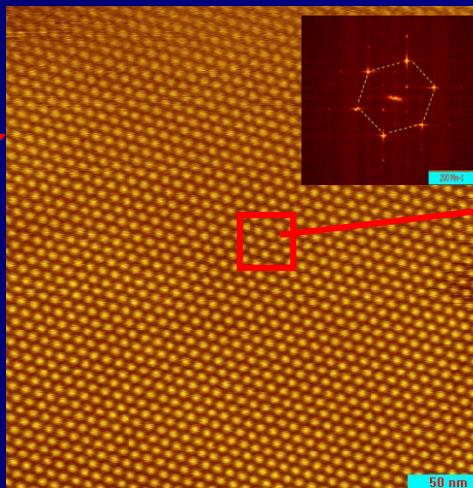
STM topography: Moiré superstructure

G. Li, et al Nature Physics (2010)

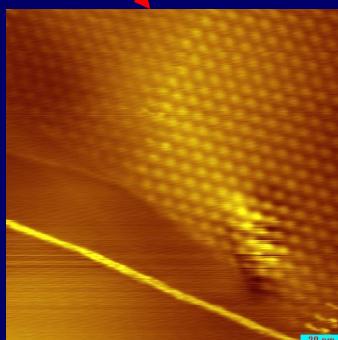
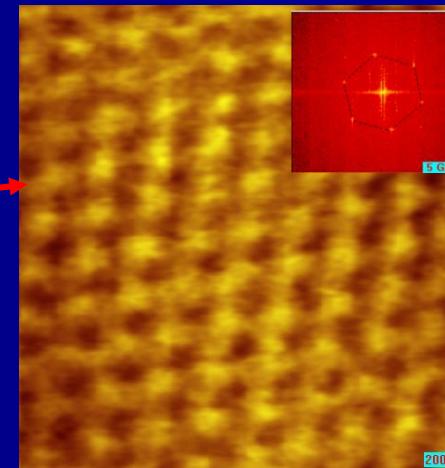
superstructure L=7.5nm $\rightarrow \theta=1.79^\circ$



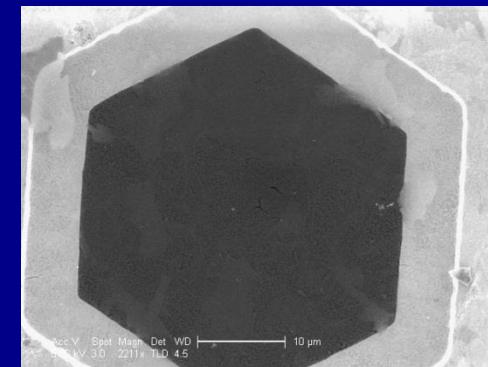
x4



x250

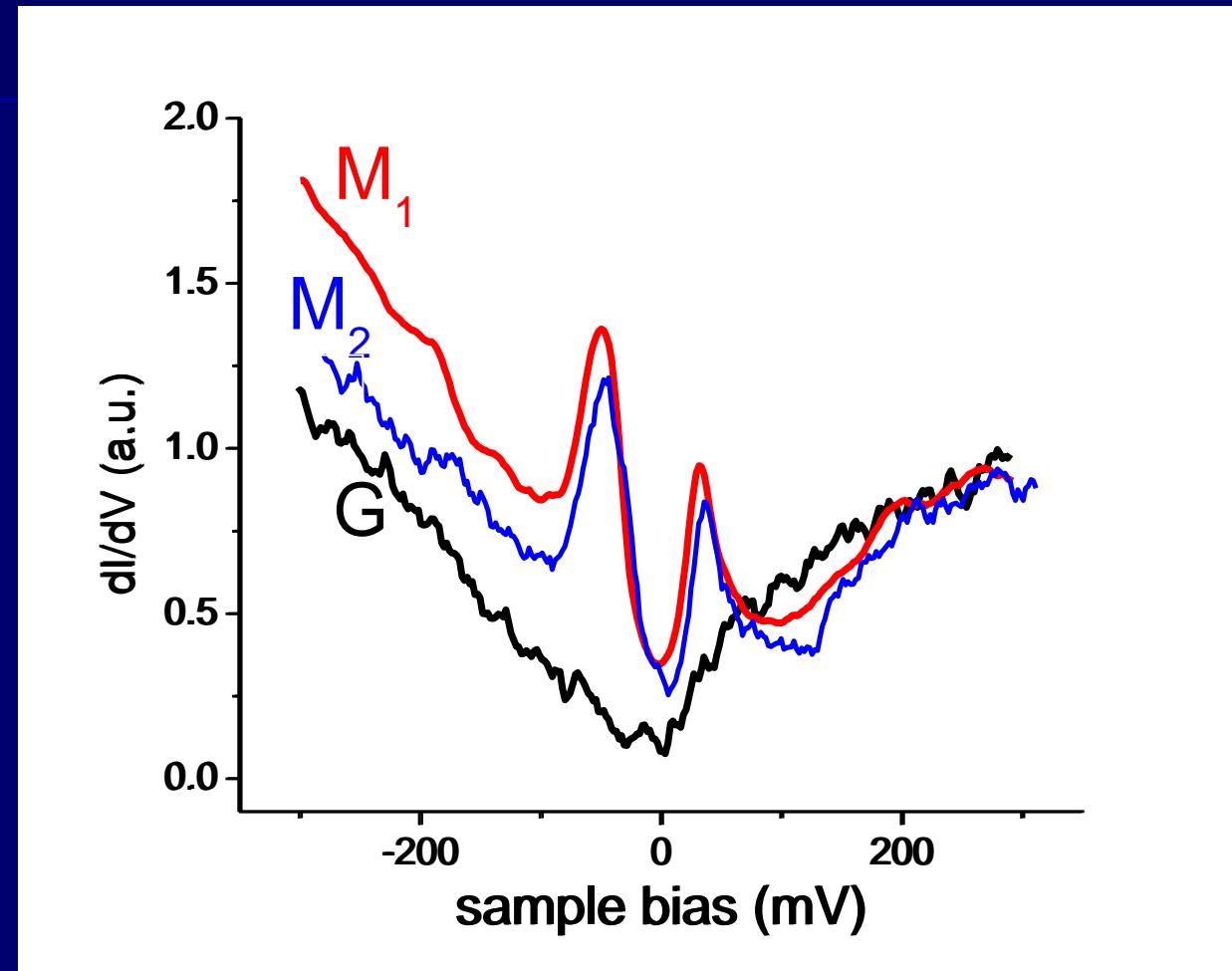
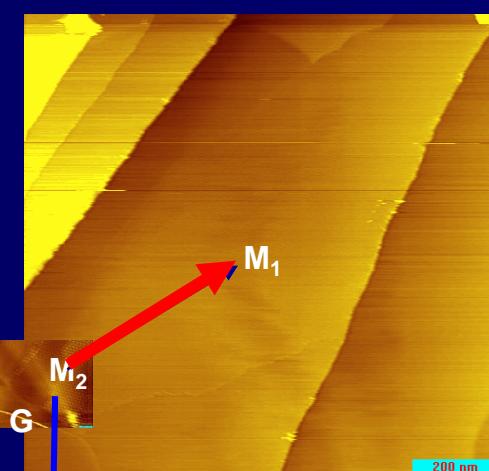
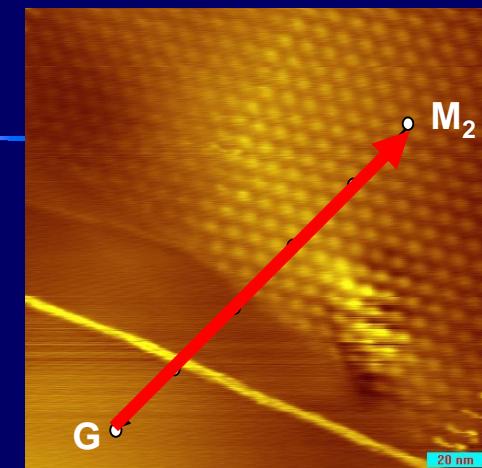


Boundary of area with superstructure



Spectroscopy Surprise

G. Li, et al Nature Physics (2010)

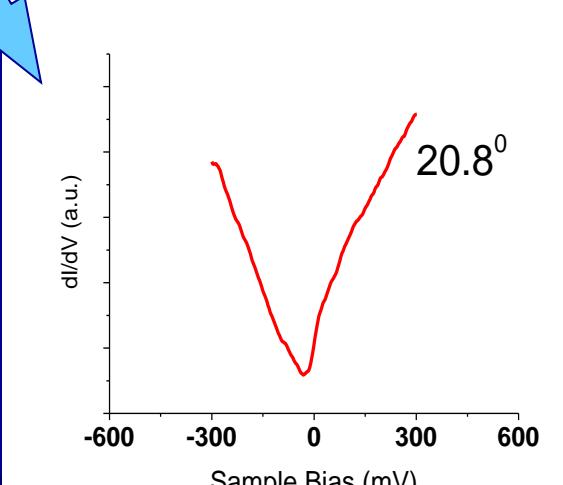
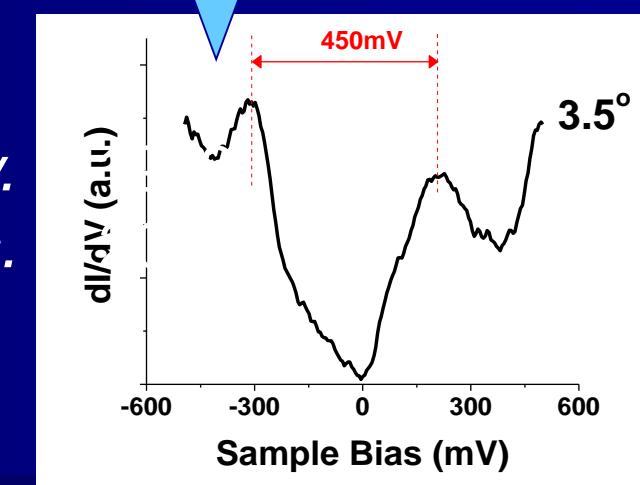
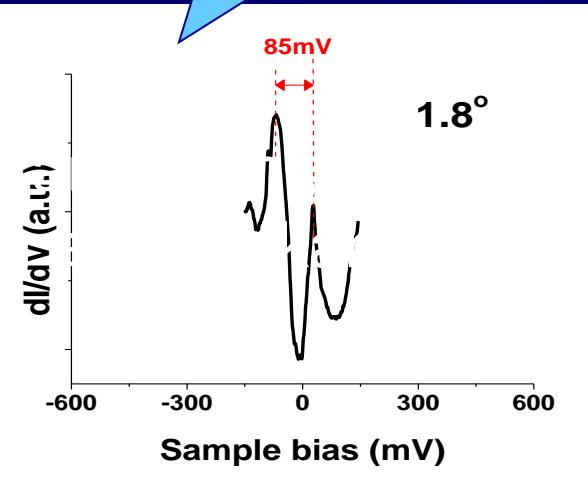
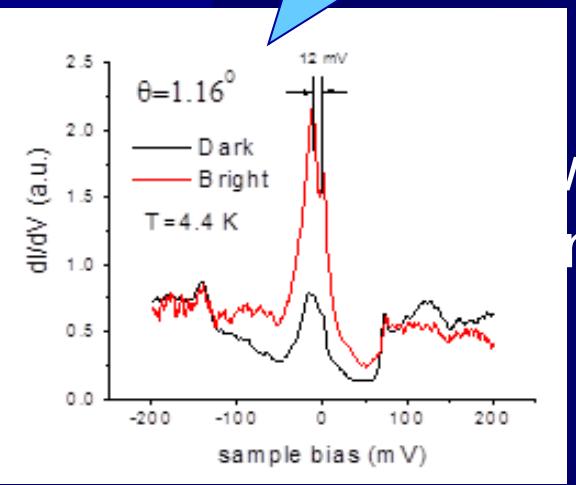
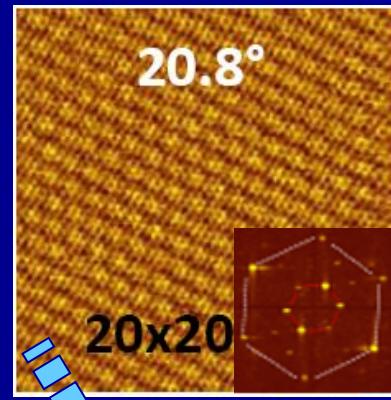
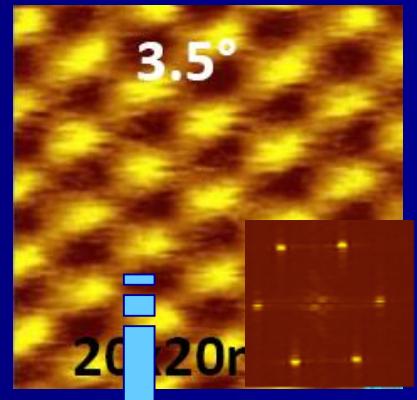
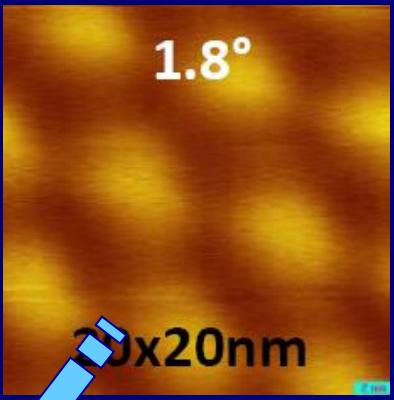
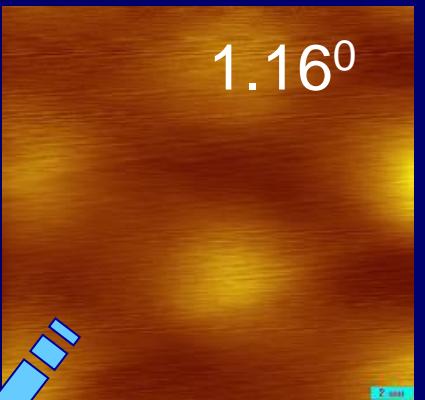


Two peak structure only in twisted region

Band structure of twisted graphene

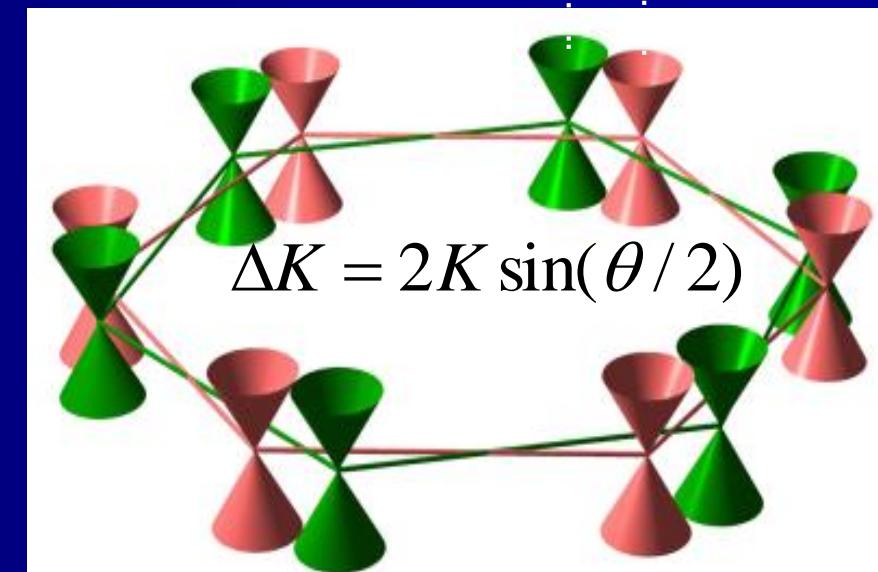
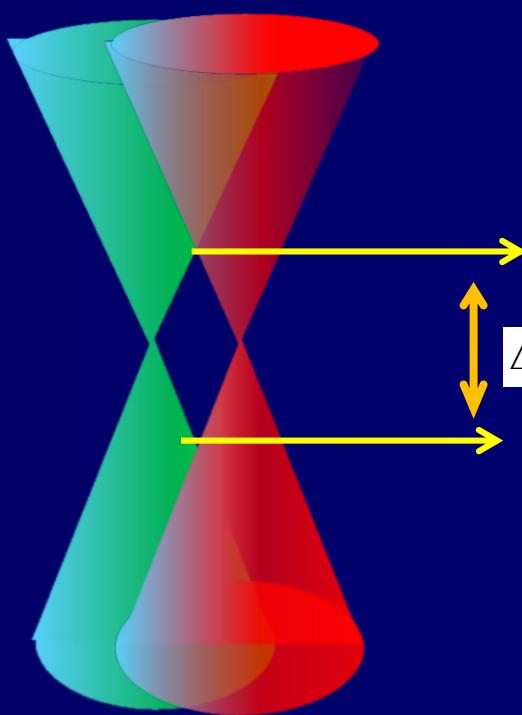
G. Li, et al Nature Physics **6**, 109 (2010)

Increasing twist angle θ



Band structure engineering with a twist

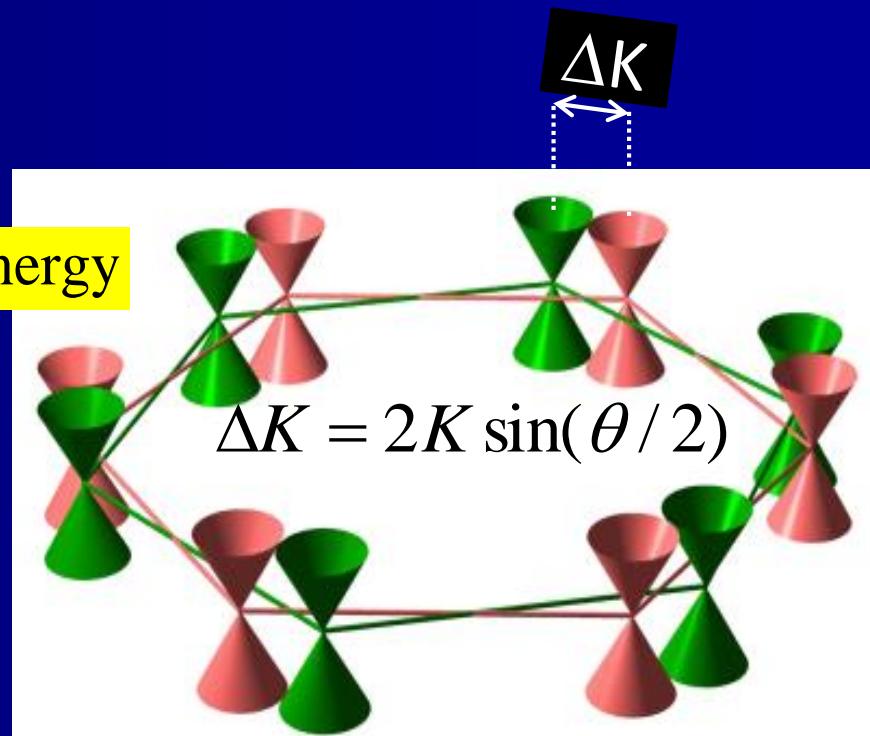
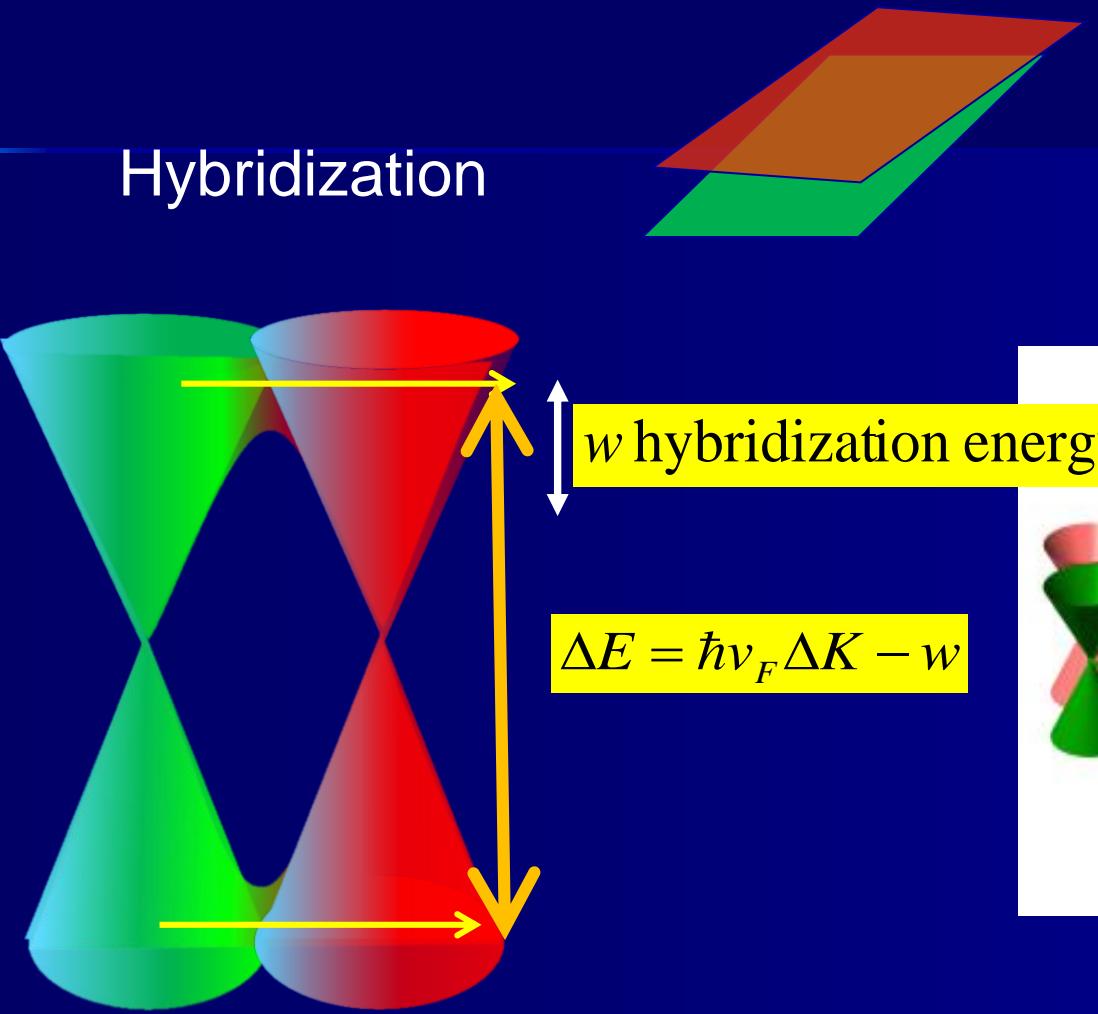
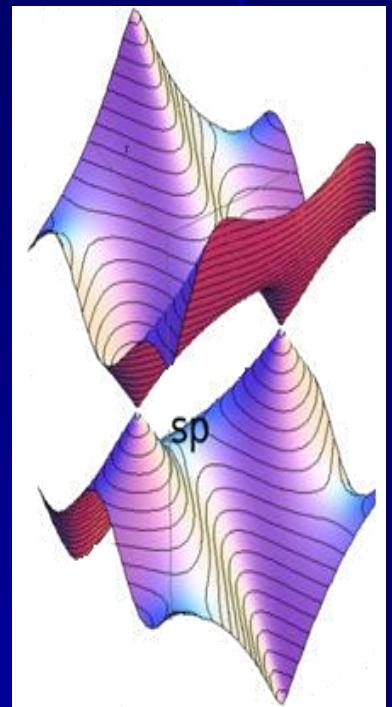
J. Lopes dos Santos, A.H. Castro Neto



Band structure engineering with a twist

J. Lopes dos Santos, A.H. Castro Neto

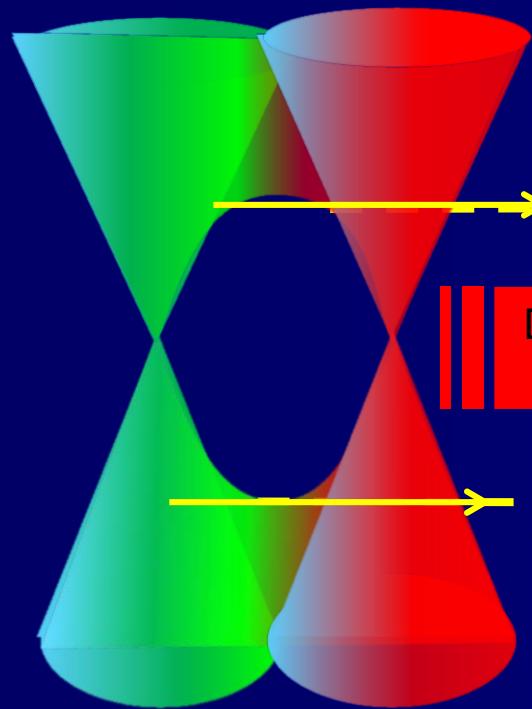
Hybridization



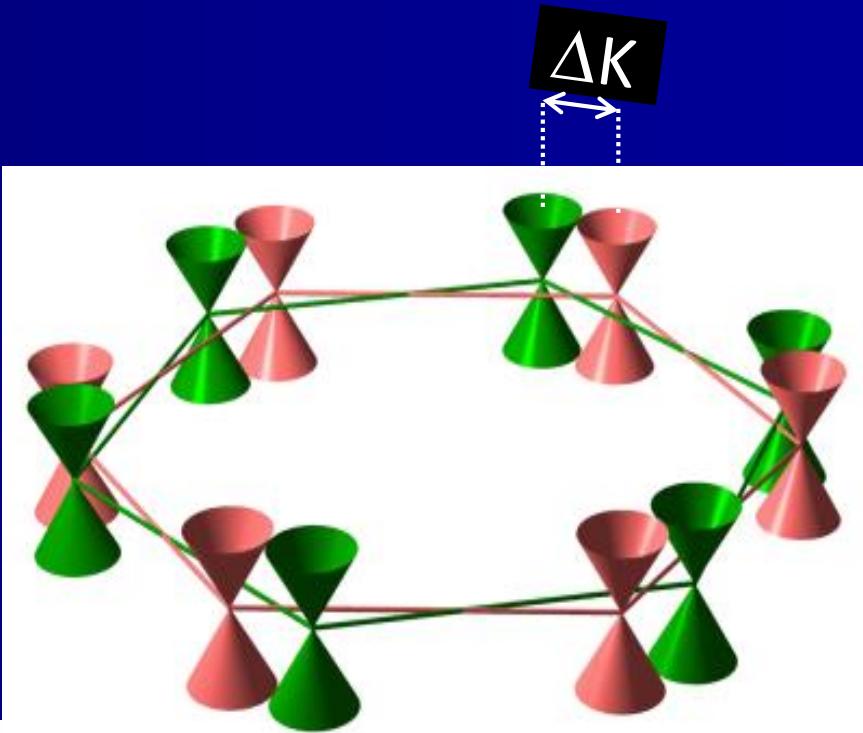
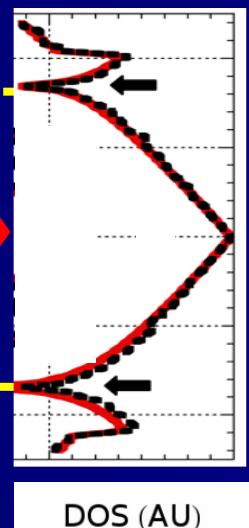
Van Hove singularities

G. Li, et al *Nature Physics* (2010)
A. Luican, et al *PRL* 106, 126802 (2011)

Hybridization



Density of
states



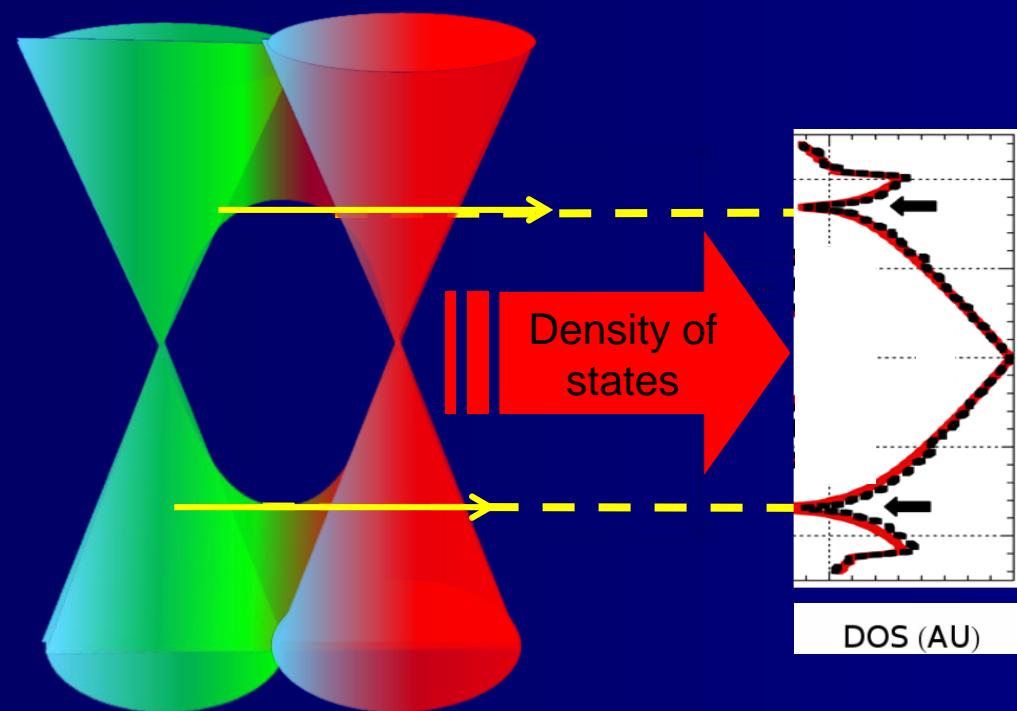
Twisted graphene
develops strong *Van Hove singularities*

E.Y. Andrei

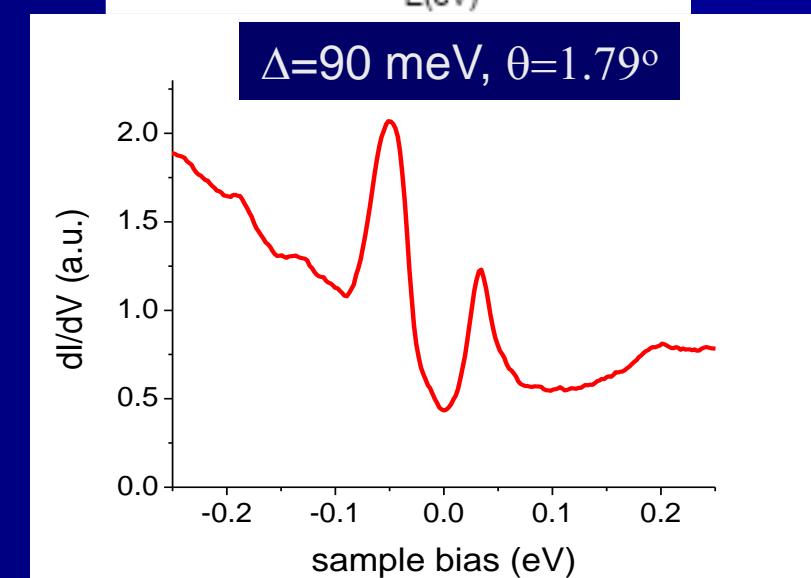
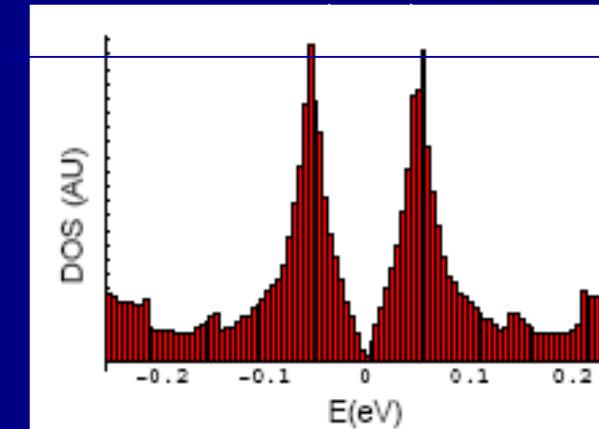


Van Hove singularities

G. Li, et al *Nature Physics* (2010)
A. Luican, et al *PRL* 106, 126802 (2011)

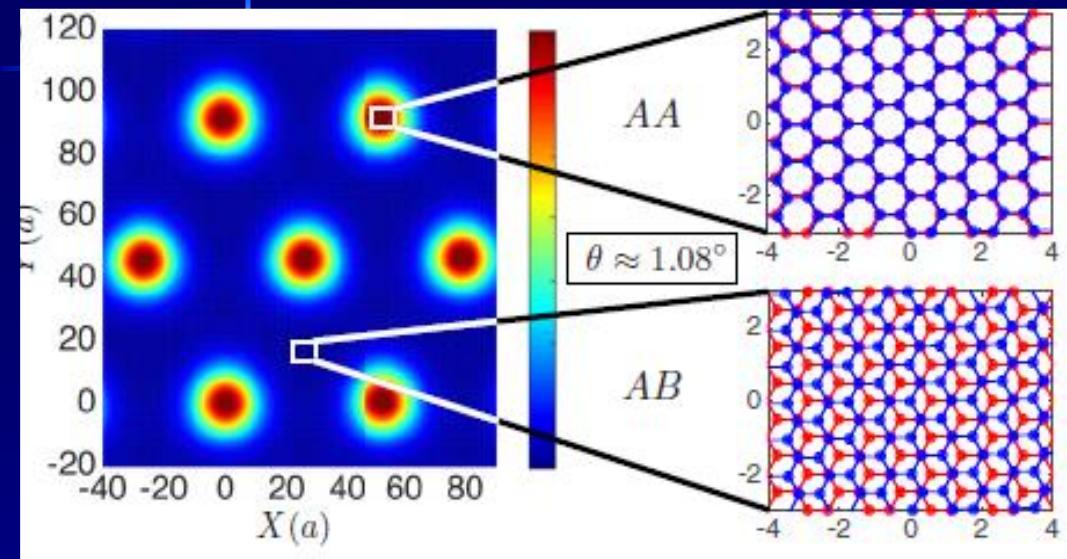


Low energy Band structure and DOS
using perturbation theory

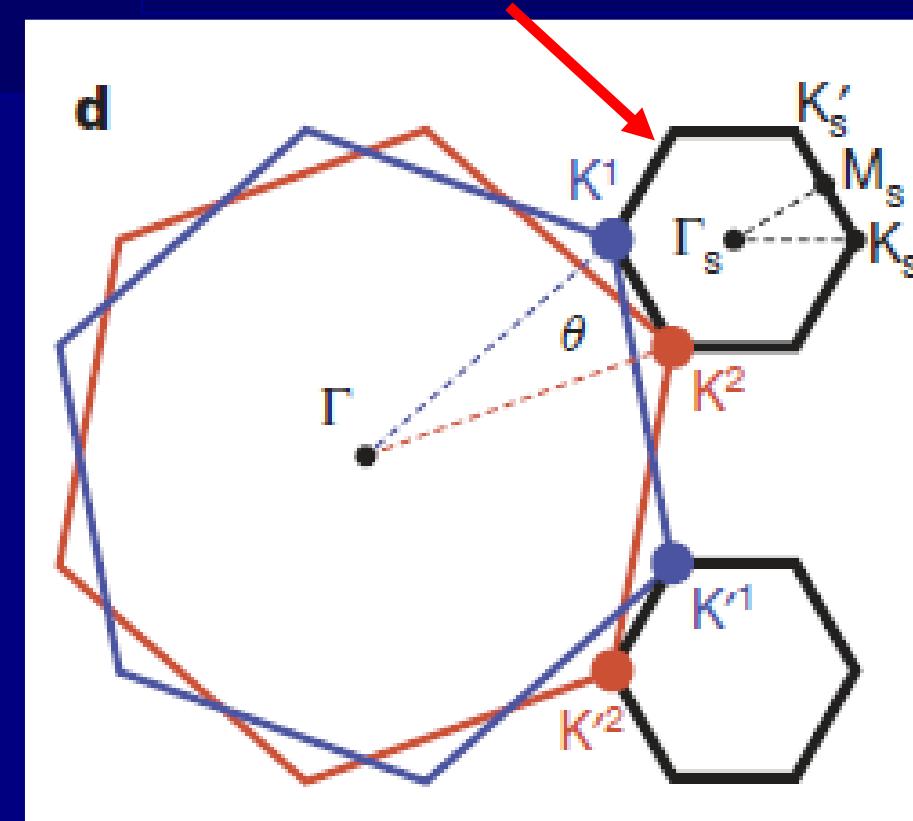


What happens at small twist angles?

DOS map

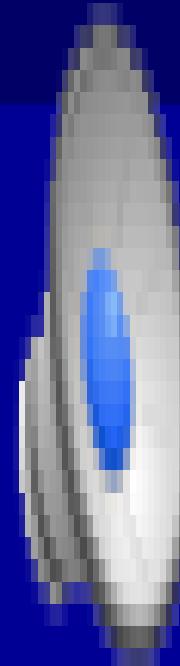
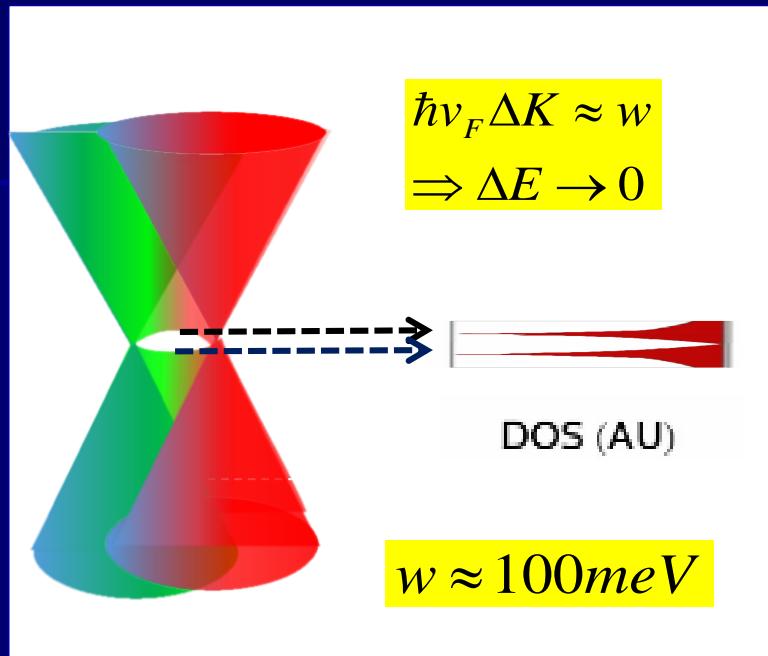
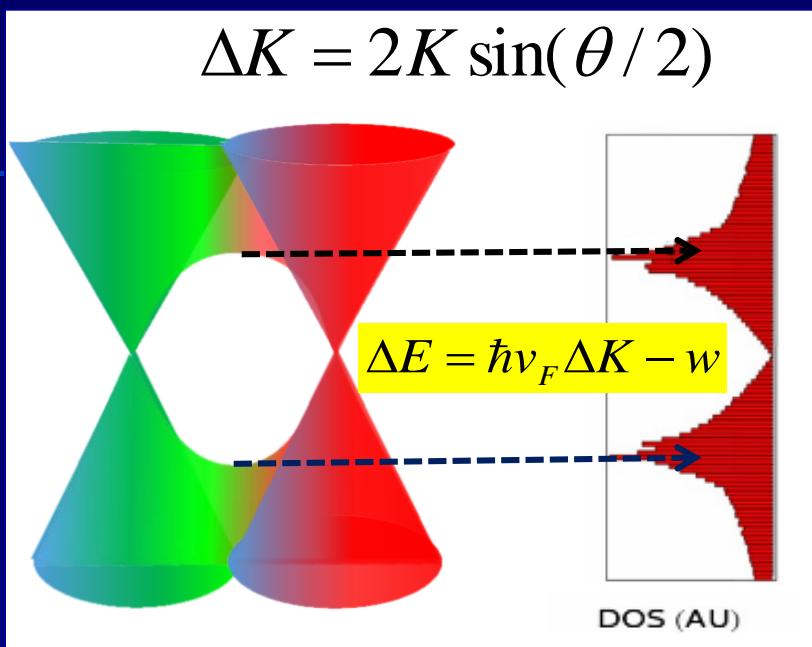


Moire Brillouin zone



Moire units cell contains 1.3×10^4 atoms!

What happens at small twist angles?



For $\hbar v_F \Delta K \approx w$ band flattens \mapsto DOS diverges: Van Hove singularities.

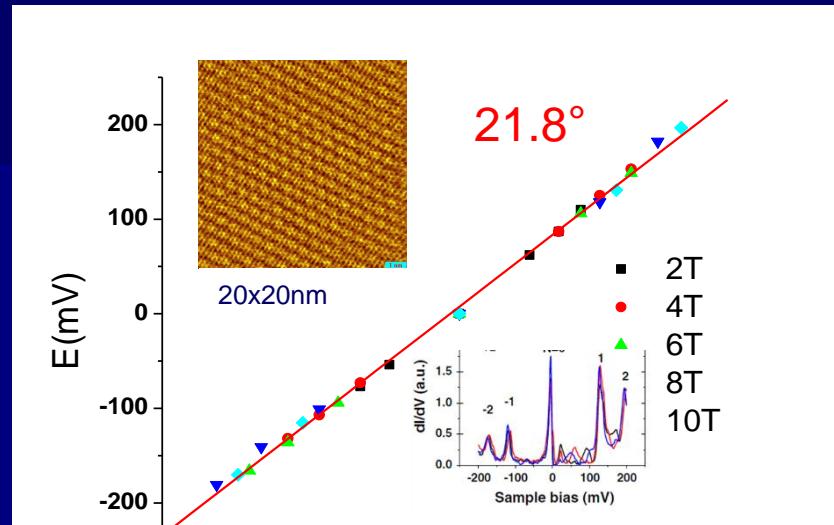
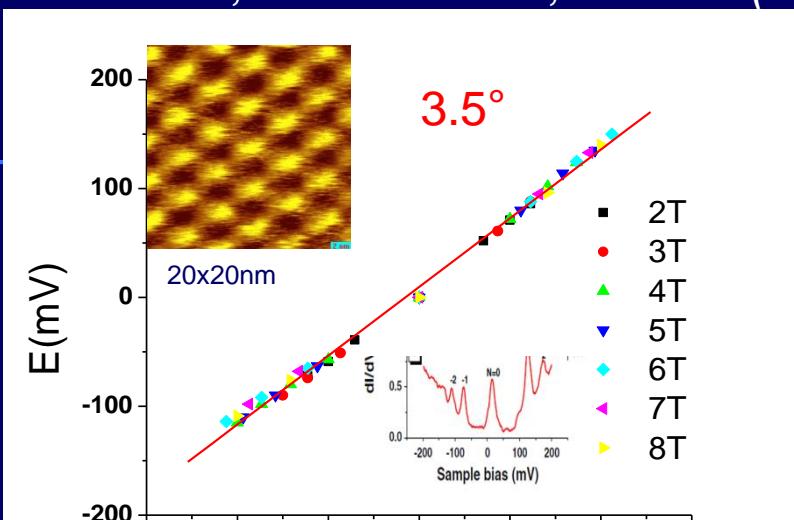
Magic angle: $\hbar v_F K \theta_M \approx w$

Using $w \sim 100\text{meV}$ $\theta_M \approx 1.09^\circ$



Fermi velocity : slowdown

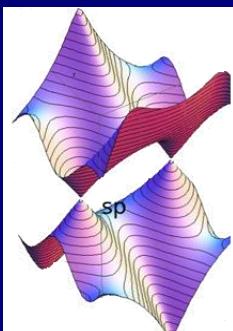
A. Luican, et al PRL 106, 126802 (2011)



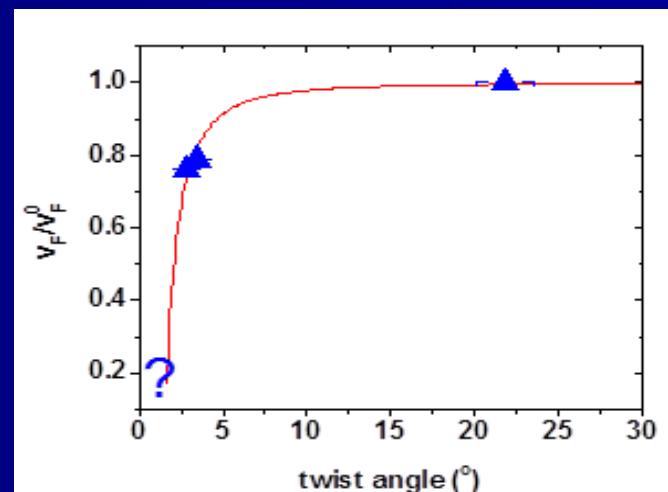
For $\theta > 10^0$

low energy band structure of twisted layers is identical to single layer

$$\frac{\tilde{v}_F(\theta)}{v_F} = 1 - 9 \left(\frac{w}{\hbar v_F \Delta K} \right)^2$$



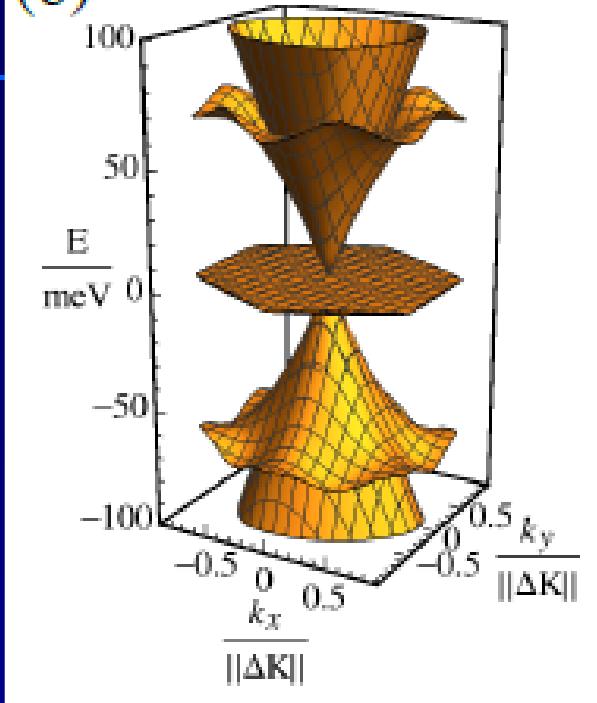
- J.M.B.L. dos Santos et al. PRL 99, 256802 (2007).
- G.T. Laissardière et al, Nanoletters ASAP (2009)
- Shalcross et al. PRL. 101, 056803 (2008)
- R. Bistritzer, and A. H. MacDonald, (2010)



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Correlation effects

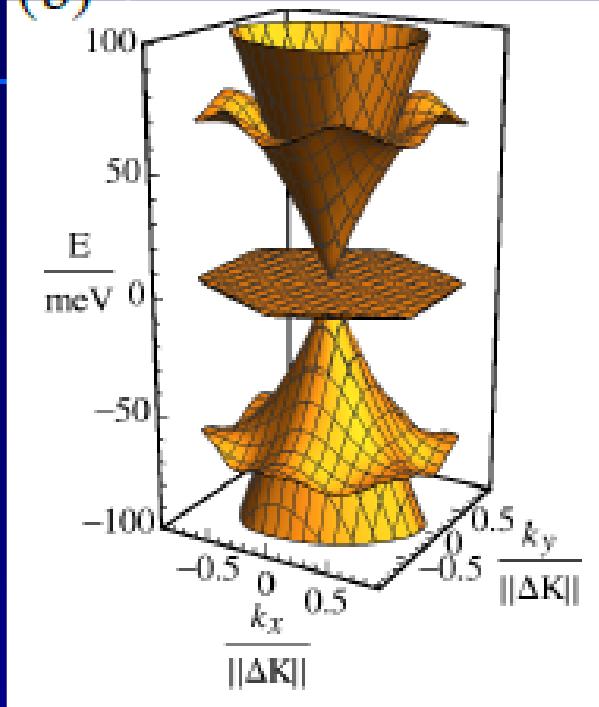


- When the energy scale of electron-electron interactions is comparable to the band-width, correlation effects become important.
- At $\frac{1}{2}$ filling (Fermi energy in middle of gap): Correlated states can emerge: superconductivity, charge density waves, antiferromagnetism, topological insulators etc.

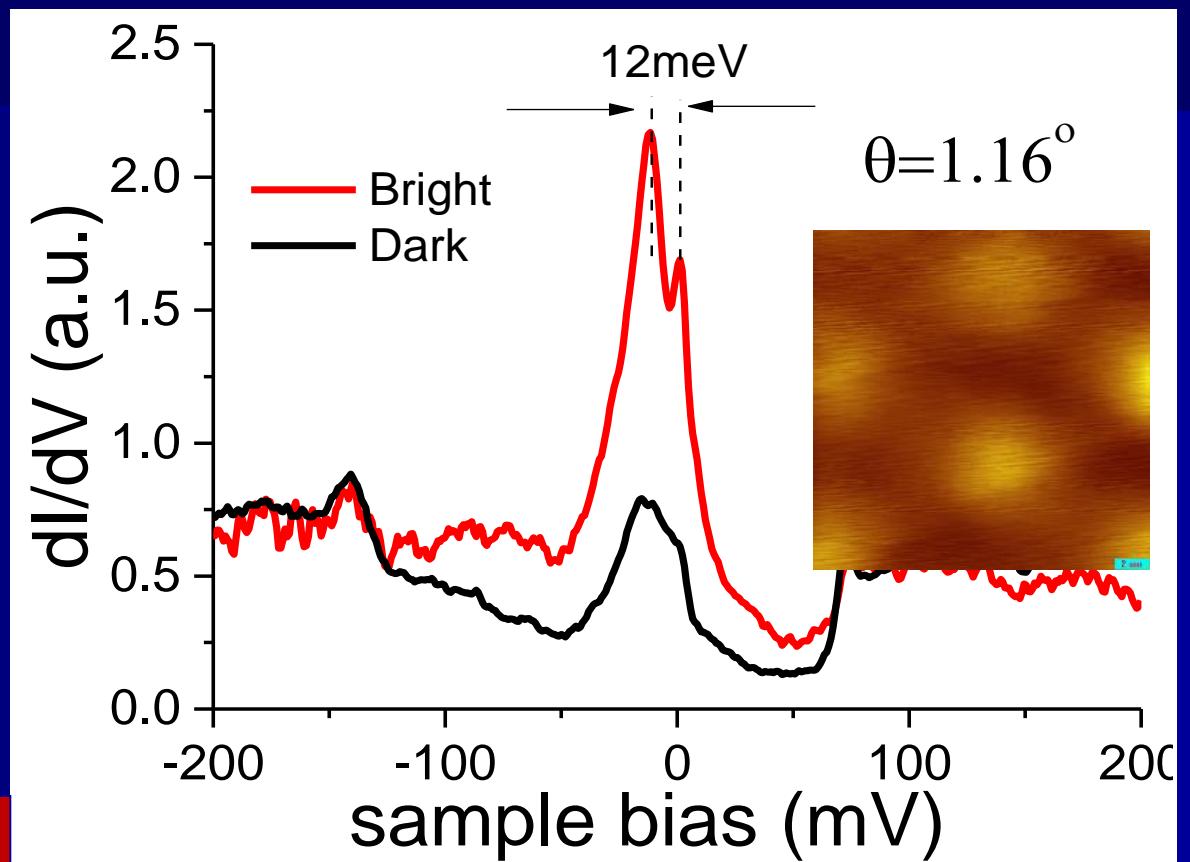
$$E_{coulomb} = \frac{e^2}{4\pi\epsilon_0\kappa\lambda^2};$$

λ moire period;
 κ dielectric constant

Correlation gap



G. Li, et al Nature Physics **6**, 109 (2010)



For $\theta = 1.16^\circ$

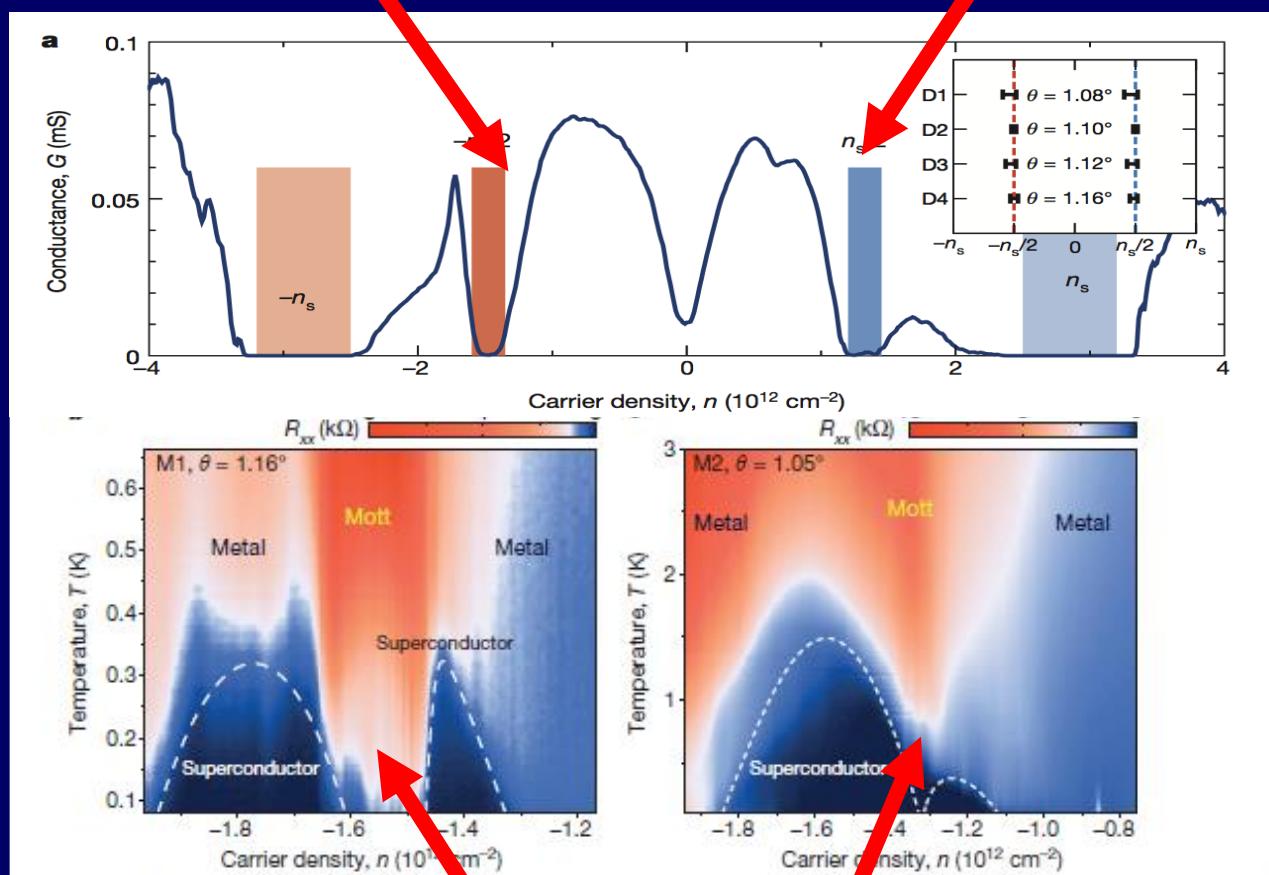
- 12meV Gap opens at the Fermi energy!
- Correlation gap – CDW?



2018 -Magic angle insulator and superconductor

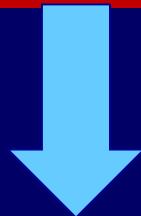
Y. Cao et al., Nature(2018)

- Half Full band – 2 electrons (holes) per moire cell.



$\frac{1}{2}$ Full band – 2 electrons (holes) per moire cell.

- $\frac{1}{2}$ Full band – insulating phase $\sim 4\text{K}$
- Insulating phase flanked by 2 superconducting domes slightly off half-filling
- Maximum $T_c \sim 1.7\text{K}$
- $T_c/E_F \sim 10^{-1} \mapsto$ strong coupling

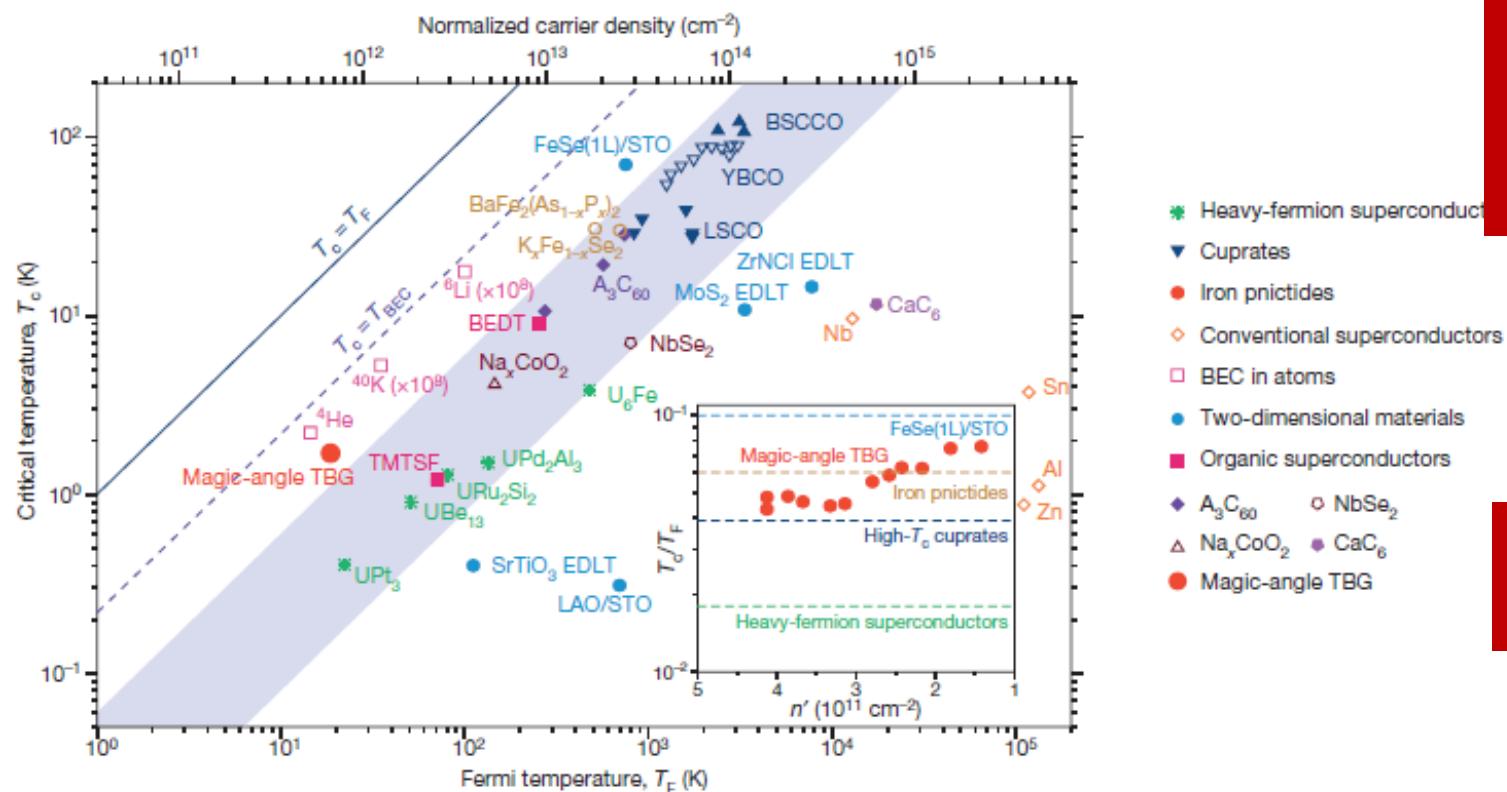


- Resembles high T_c superconductors
- BUT tunable doping and T_c



Strongly coupled superconductor

Y. Cao et al., Nature(2018)



- $\frac{1}{2}$ Full band – insulating phase $\sim 4\text{K}$
- Insulating phase flanked by 2 superconducting domes
- $T_c/E_F \sim 10^{-1} \mapsto$ strong coupling



- Resembles high T_c superconductors
- BUT tunable doping and T_c

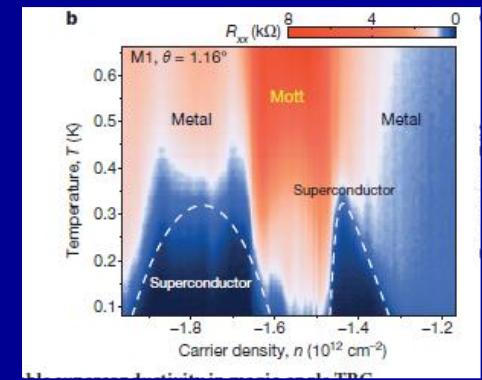
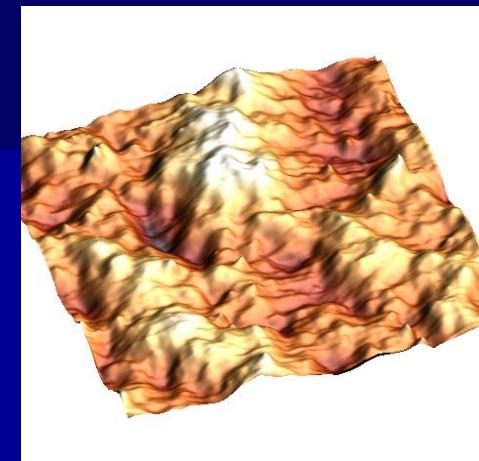
OPEN QUESTIONS:

- Pairing mechanism
- Gap symmetry
- Nature of insulating phase



Summary of part IV

- Kondo screening in graphene occurs above a critical coupling strength
 - Magnetic moments in graphene can be tuned with gating or local curvature
 - If coupling strength is non-uniform global measurements are misleading
-
- Band structure of bilayer graphene can be tuned with twist angle
 - At small twist angles the DOS develops Van-Hove singularities
 - At the “magic angle” $\theta \sim 1.1^\circ$ a flat band forms at the charge neutrality point
 - At half filling the flat band develops strong correlations resulting in an insulating phase flanked by superconducting domes.



2D materials are cool!